

One man's treasure another man's treasure?

- Semiconductor radiation detectors

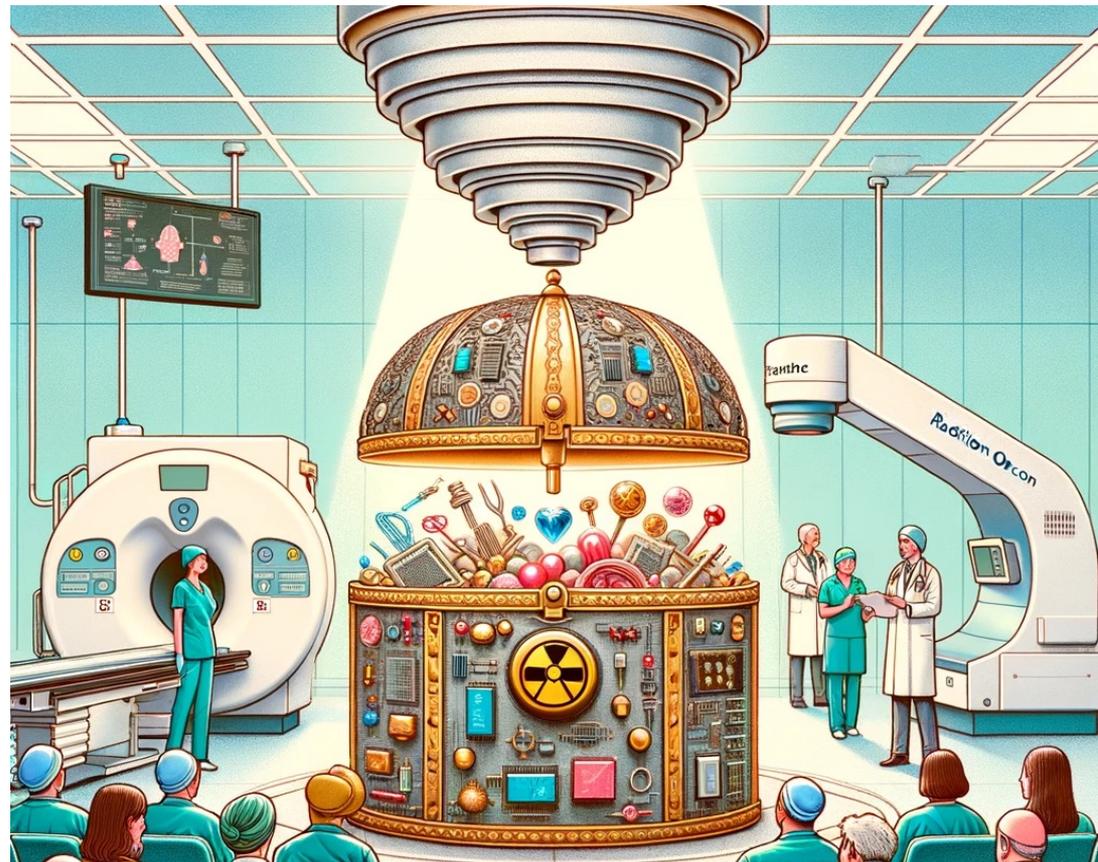
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Residency 2023~2024

Rotation Mentor: Xiao Wang

RUTGERS

Robert Wood Johnson
Medical School



Solid radiation detectors



QED diode (SunNuclear)



Nal(Tl) gamma spectrometer

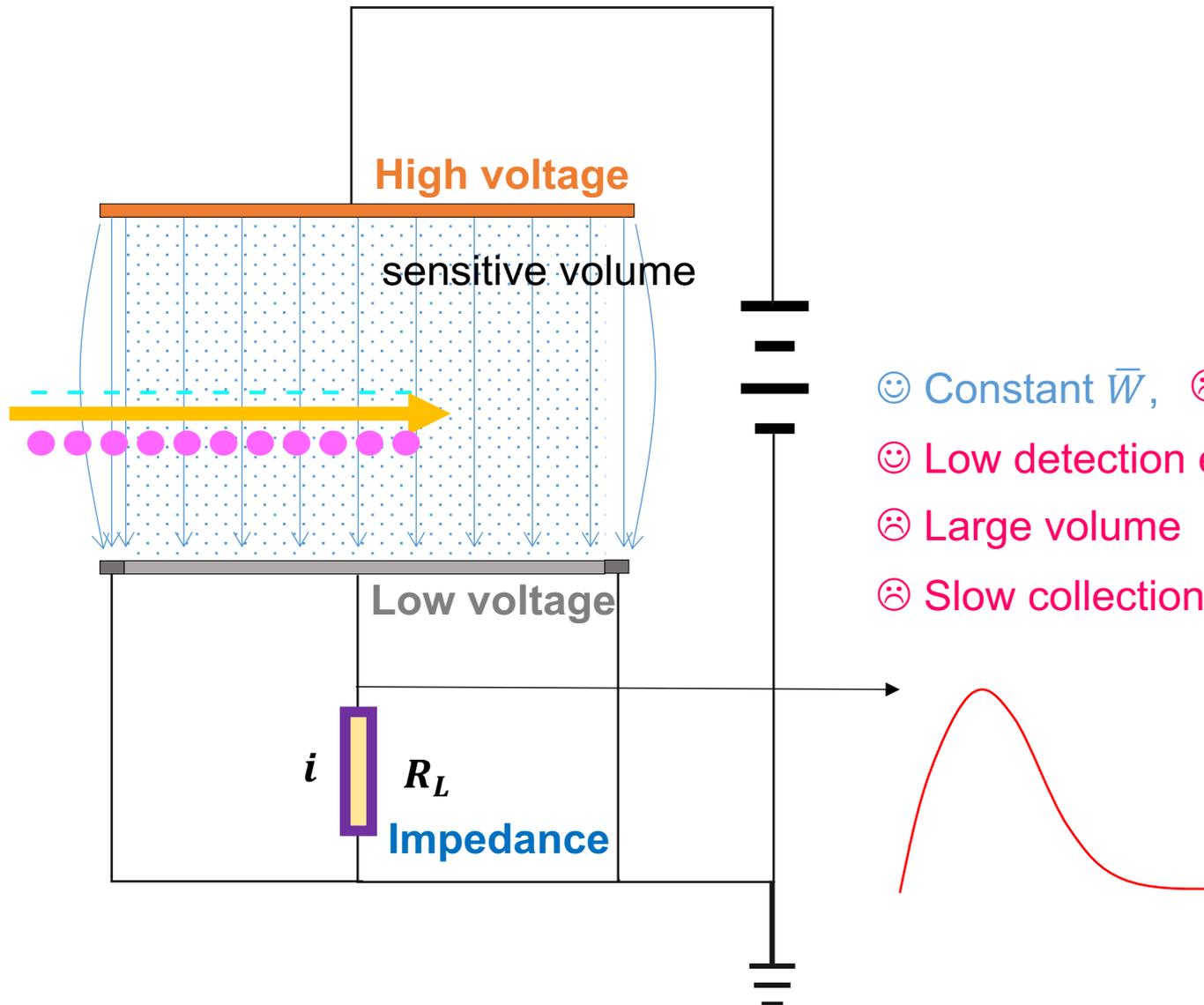


Photon-counting Detector (Varex)



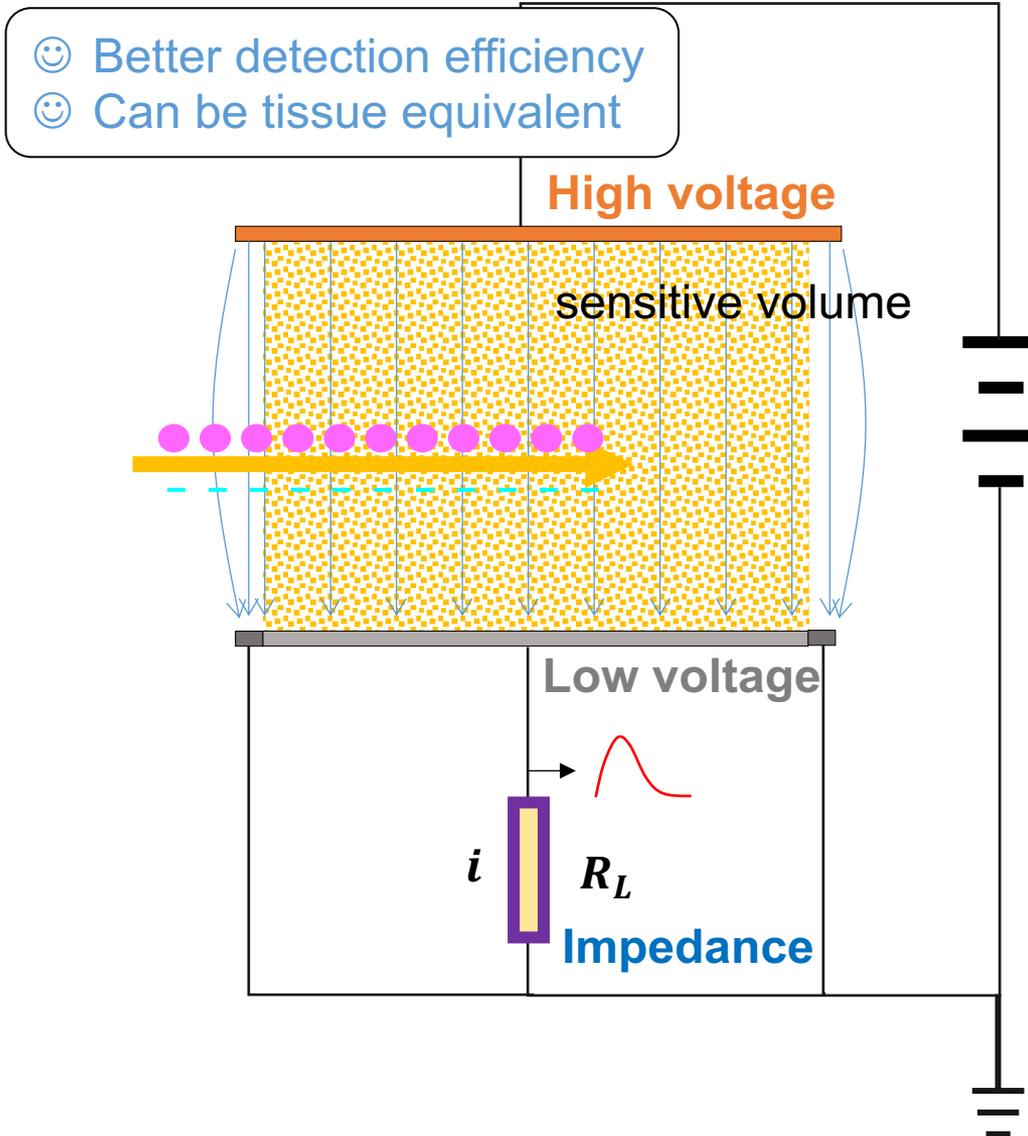
Photon-counting CT (Siemens)

“Gas” ion chamber



- ☺ Constant \bar{W} , ☹ but > 30 eV
- ☺ Low detection efficiency
- ☹ Large volume
- ☹ Slow collection

“Solid” ion chamber



- ☺ Better detection efficiency
- ☺ Can be tissue equivalent

Insulator

- ☺ Smaller \bar{W}
- ☺ Low leakage current
- ☹ Undesired electronic property

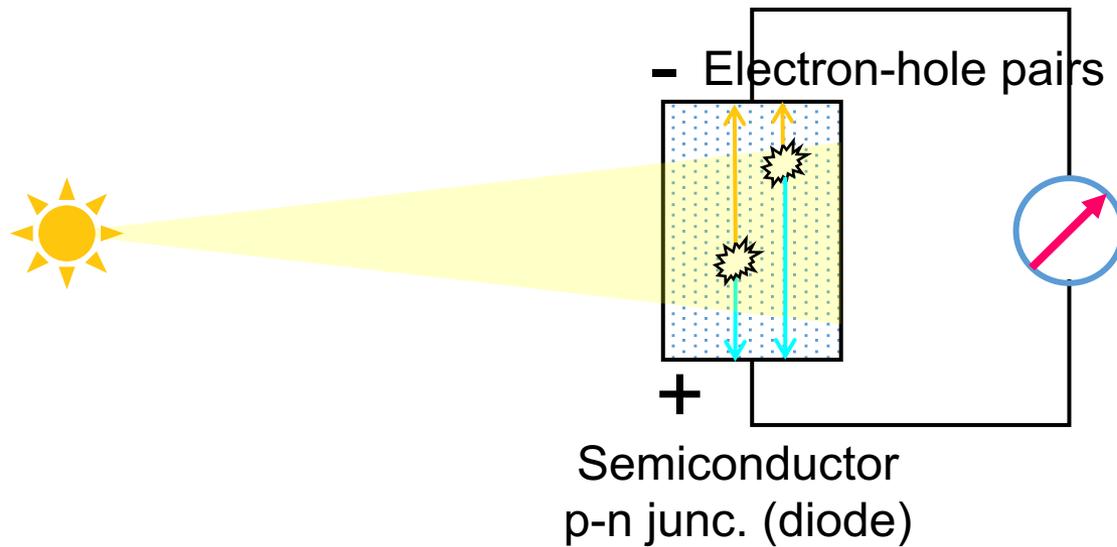
Intrinsic Semiconductor

- ☺ Relatively \bar{W} , < 6 eV
- ☺ High charge carrier mobility
- ☹ Leakage current

Diode (p-n junction)

- ☺ High impedance
- ☺ Goodness of semiconductor

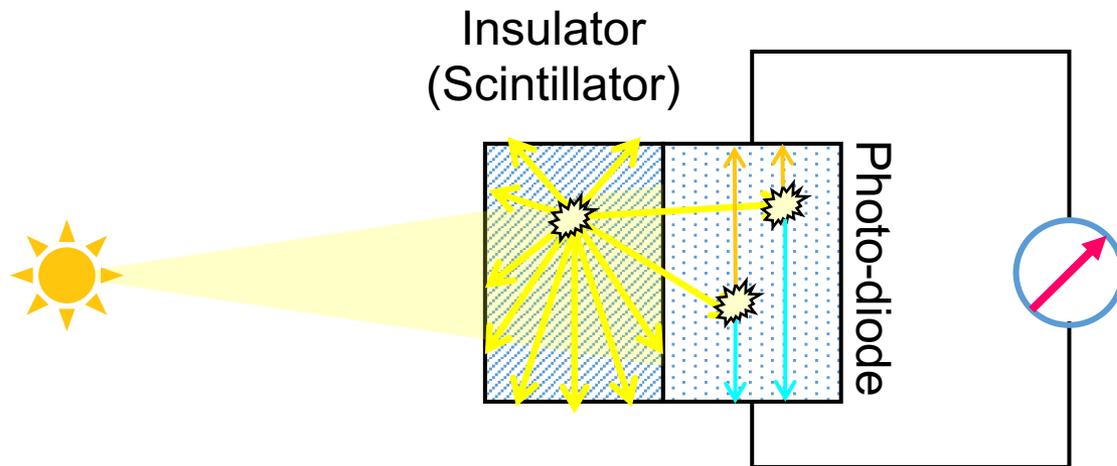
Solid detector (I): Direct Conversion



☹ Still low detection efficiency

Solid detector (II): Scintillation

Dr. Wilhelm Röntgen 1895

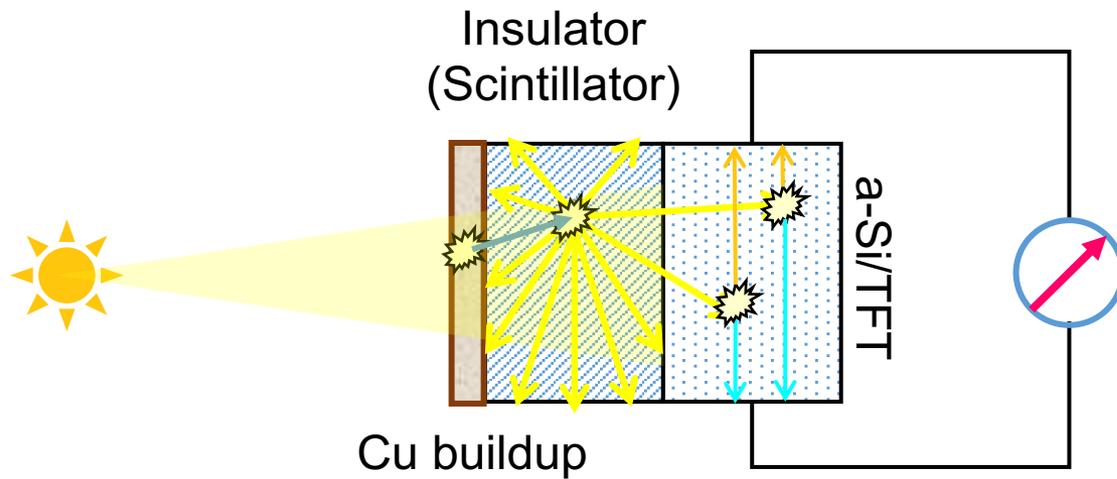


☺ Good efficiency

☹ After-glow (slow collection)

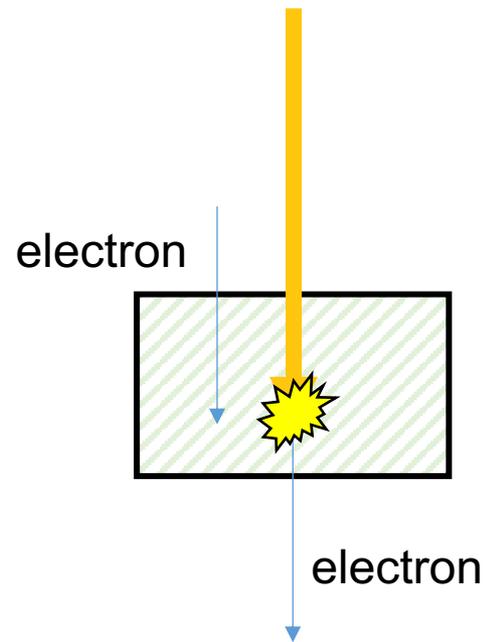
☹ SNR loss

Solid detector (III): Scintillation



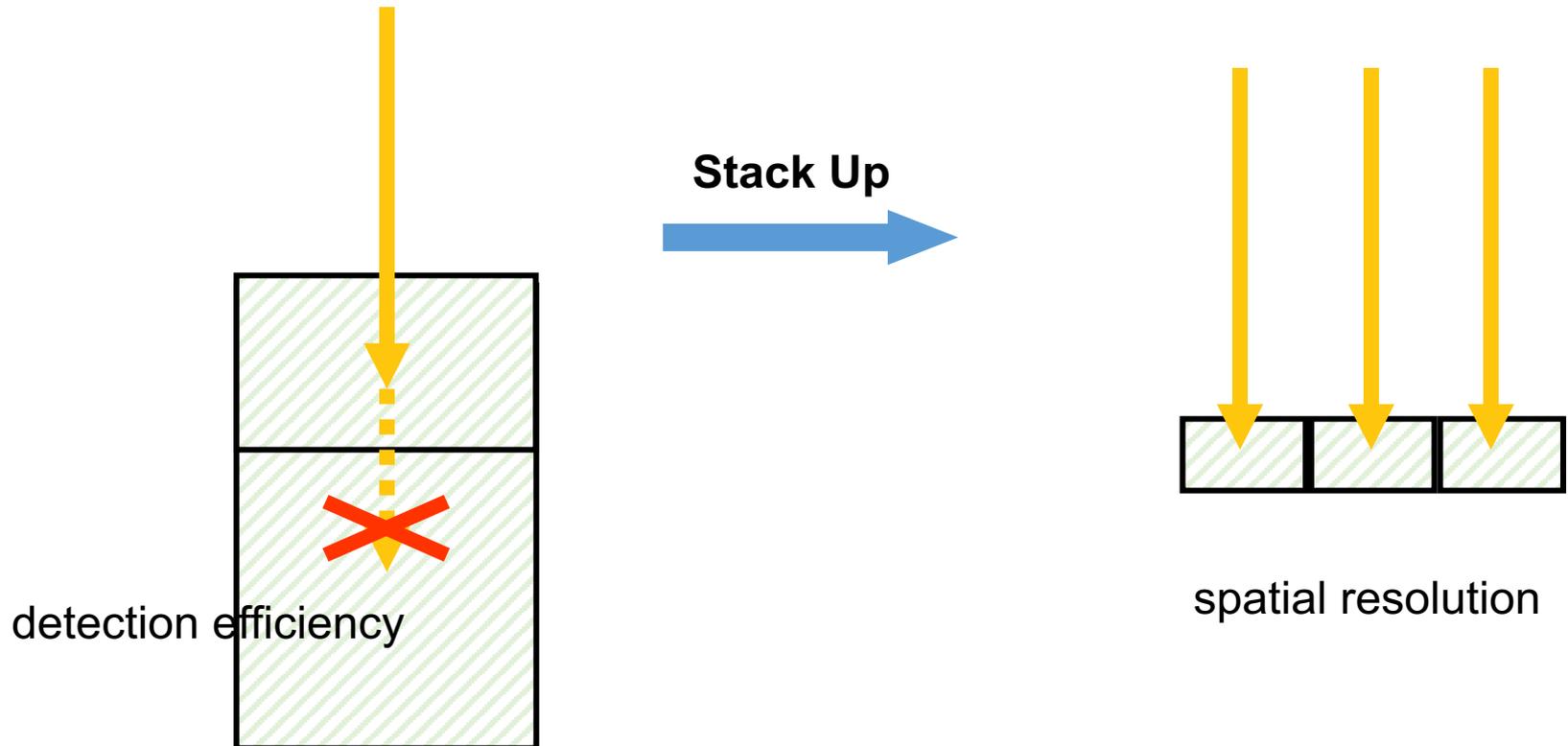
Portal Dosimetry, MV Imaging

- General principle: energy transfer under CPE

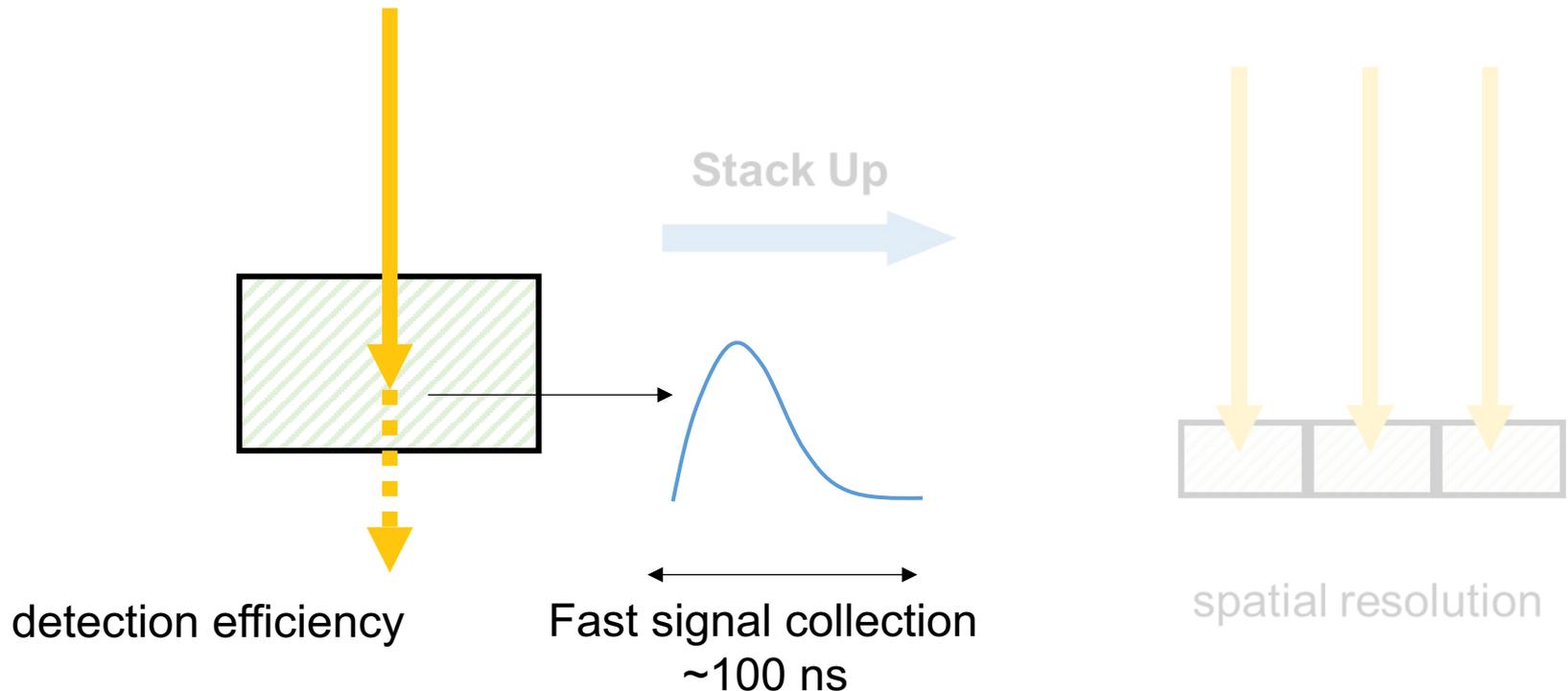


$$\text{Dose} = \frac{\text{Energy}}{\text{Mass}}$$

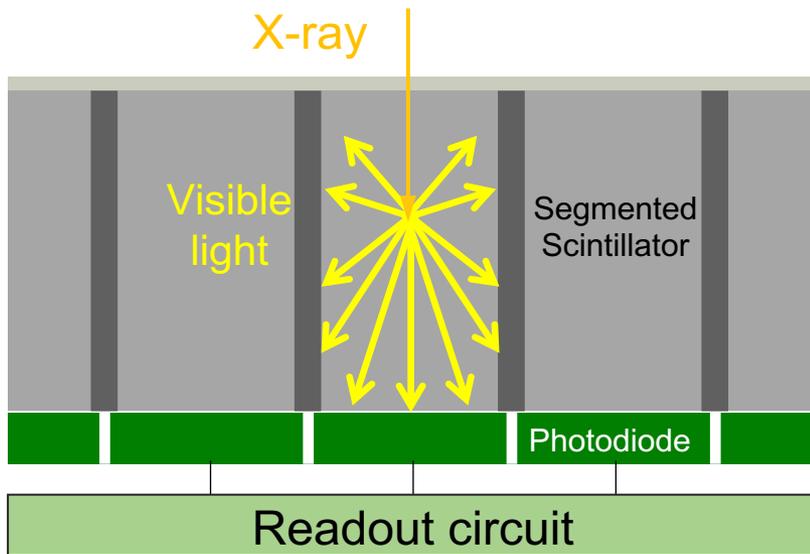
- General principle: Record photon fluence



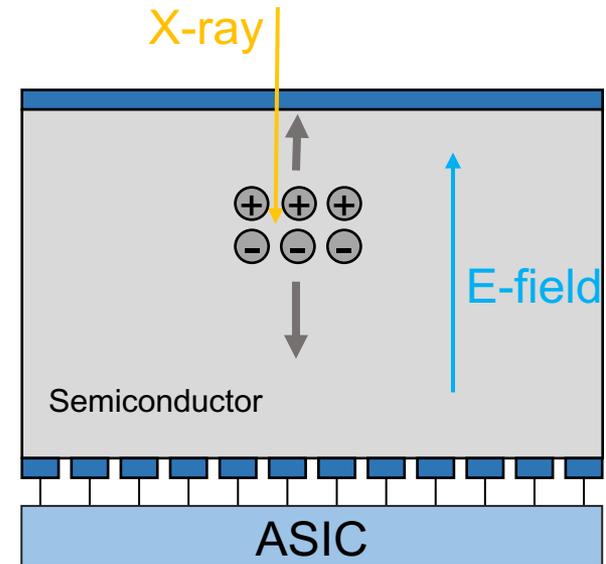
- General principle: Count the photon!



Two important x-ray imaging detectors

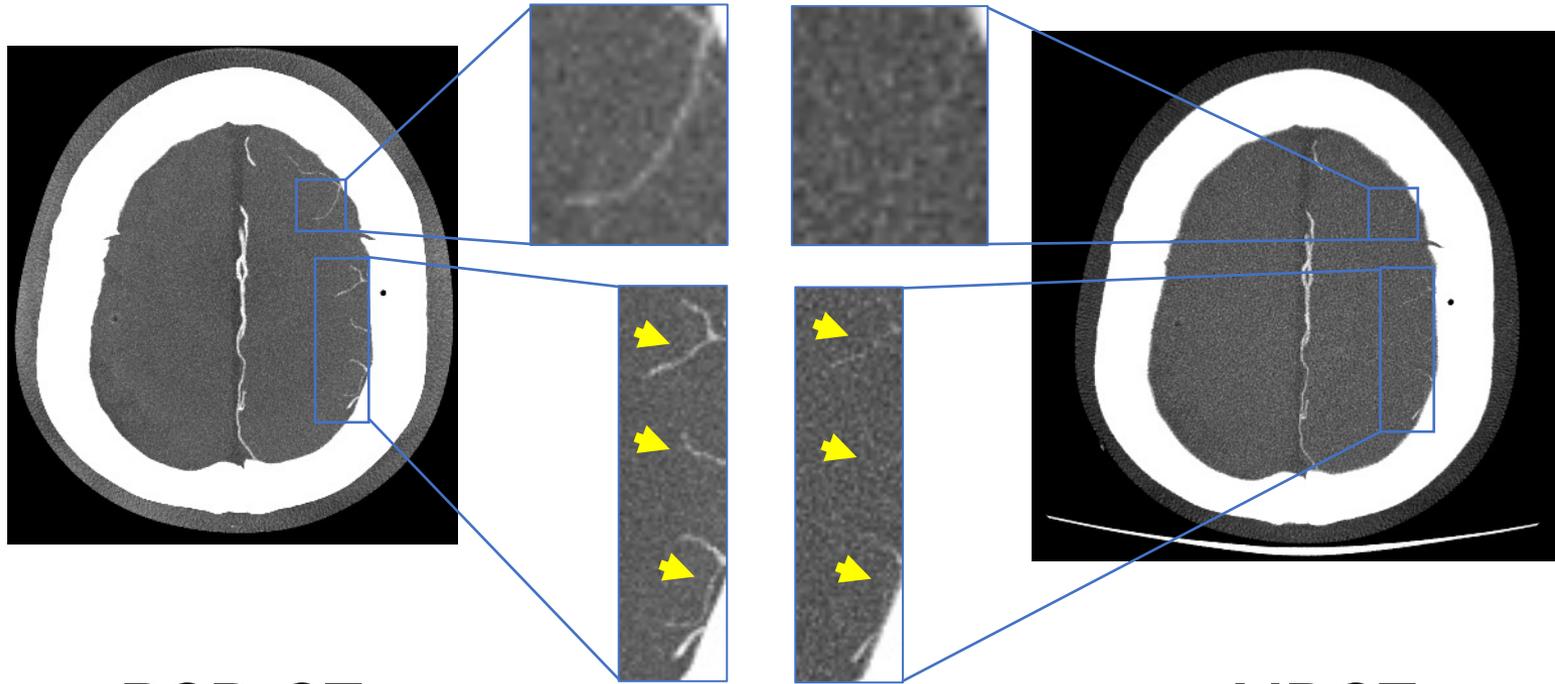


Scintillation Detector
Diagnostic/SIM CT (Gadox)
CBCT (CsI)
EPID (Gadox)



“Photon Counting” Detector
(CdTe, CdZnTe, Si)

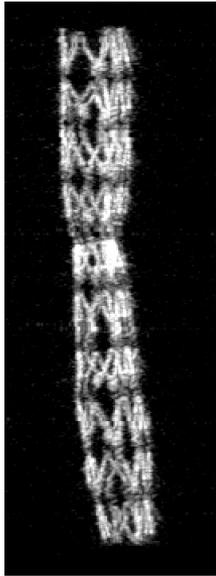
Comparison



PCD-CT
(Semi-conductor)

MDCT
(Scintillation)

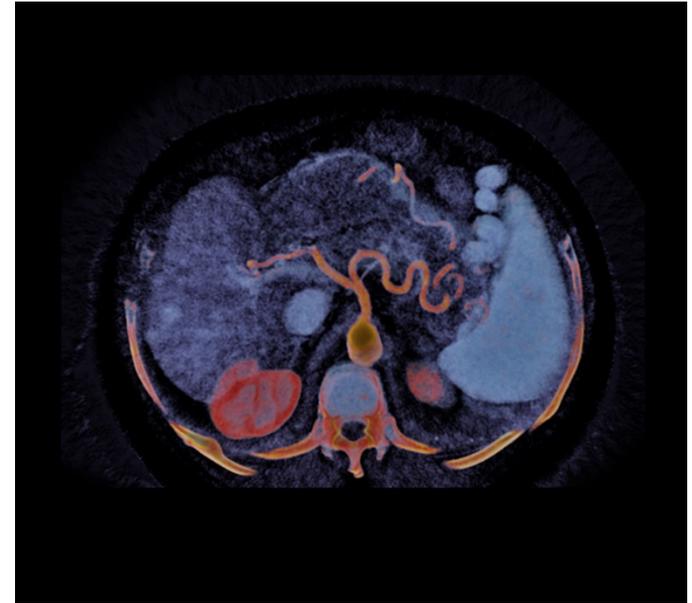
One man's treasure



PCD-CT
Highest
resolution



CBCT
Highest
resolution



Iodine map
material decomposition

☺ High spatial resolution

☺ Better contrast

☺ Energy resolving capability

Our Clinic

In-vivo dosimetry (TBI, ...)

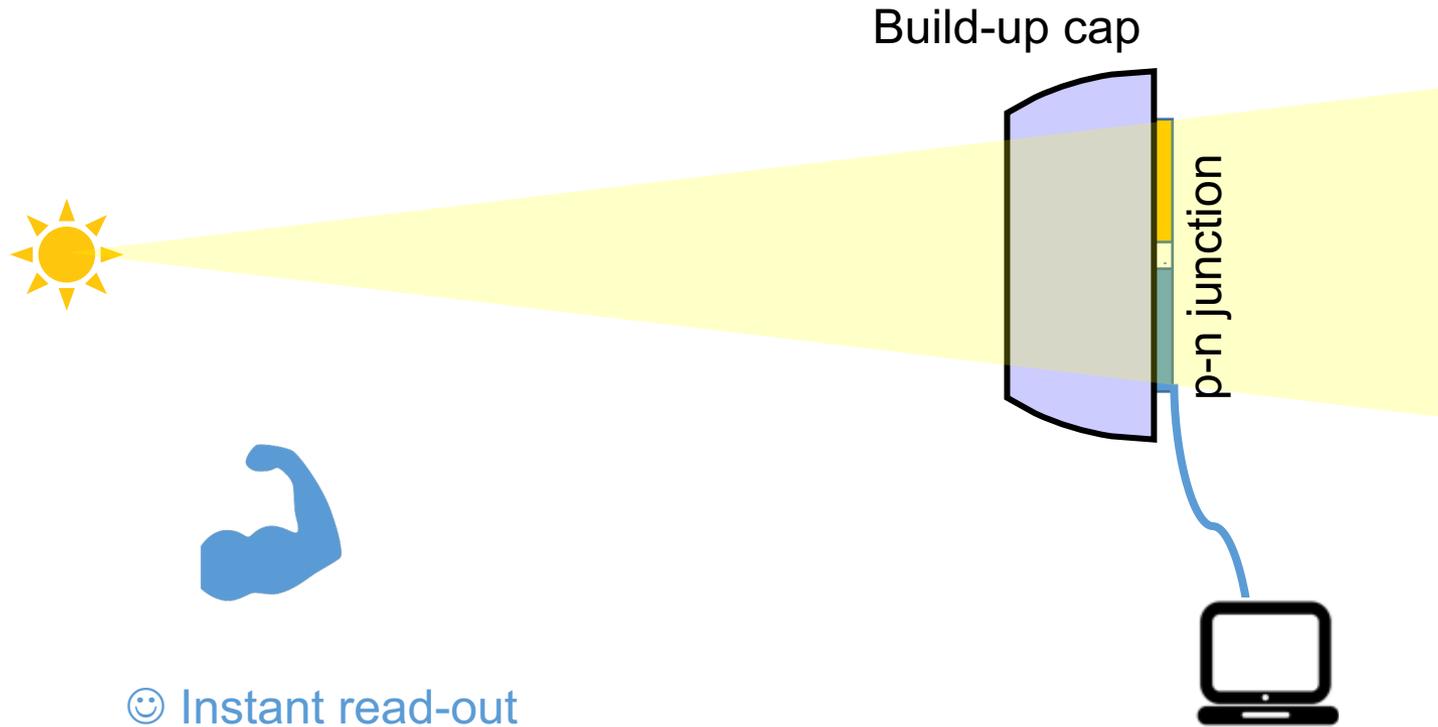
Major Use

Measure PDD
QA devices (Delta4, daily
QA3, IC profiler)



Our Boy!

Is it another man's treasure?



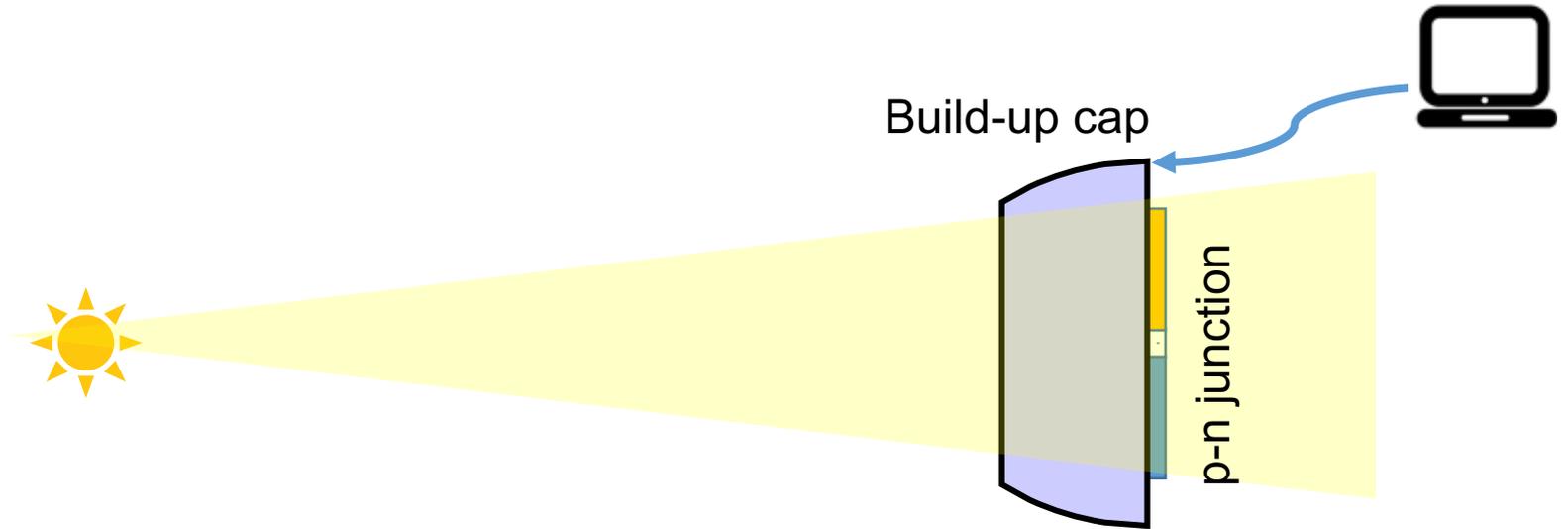
- ☺ Instant read-out
- ☺ Small volume
- ☺ SNR

In reality ...

RUTGERS



Let's be fair ...

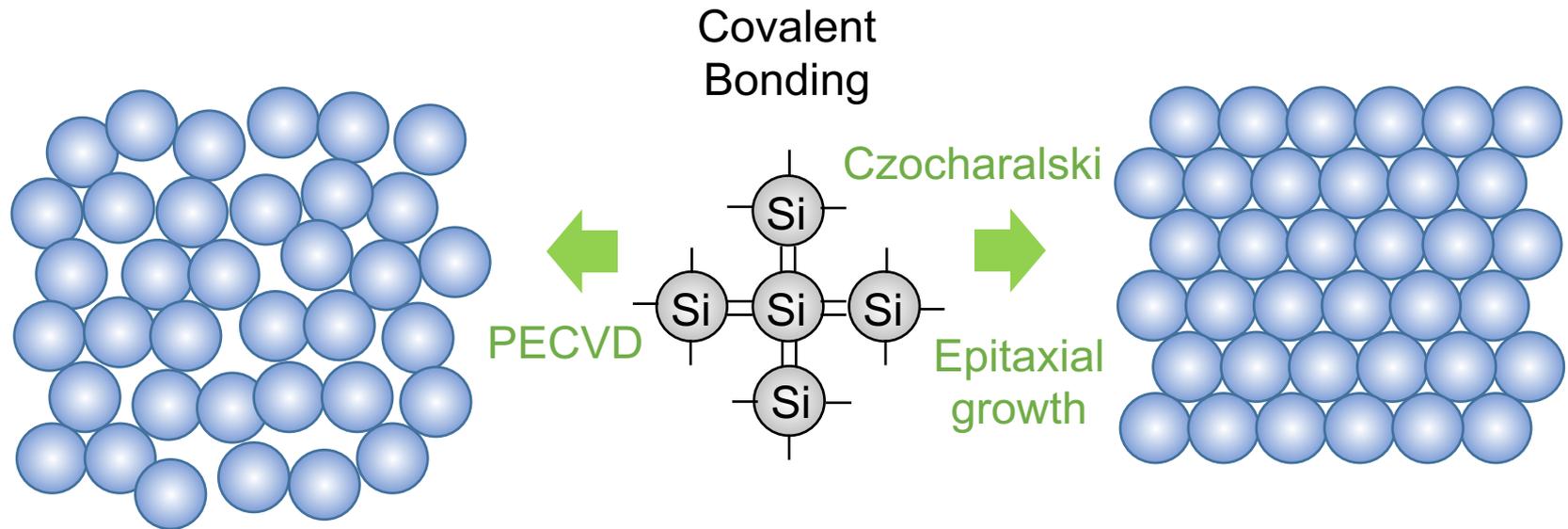


- ☺ SNR
- ☺ Small volume
- ☺ Instant read-out



- ☹ Temperature dependence
- ☹ Dose rate dependence
- ☹ Energy dependence
- ☹ Orientation dependence
- ☹ Radiation damage

Crystal Structure



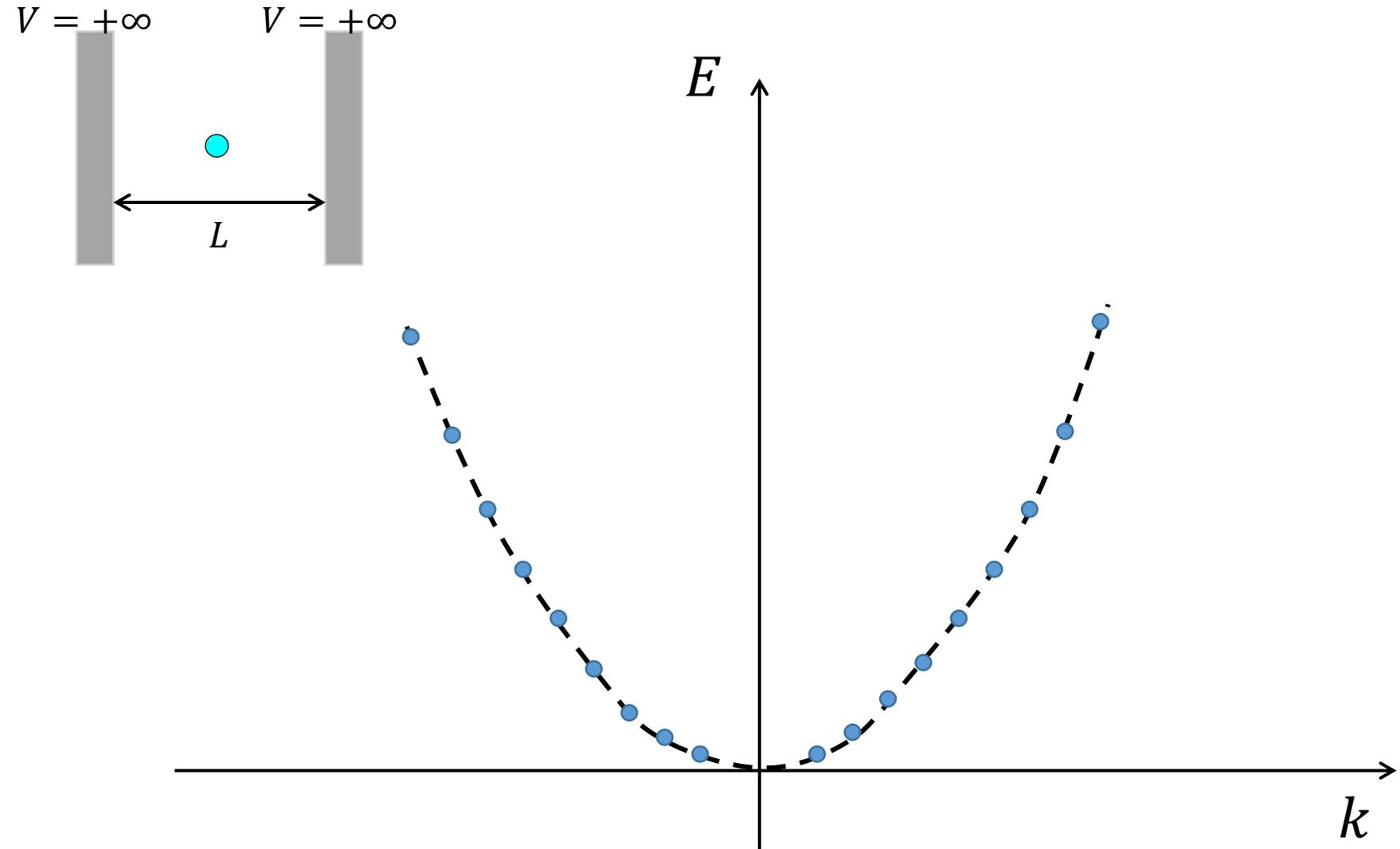
better electronic property

EPID (large panel)

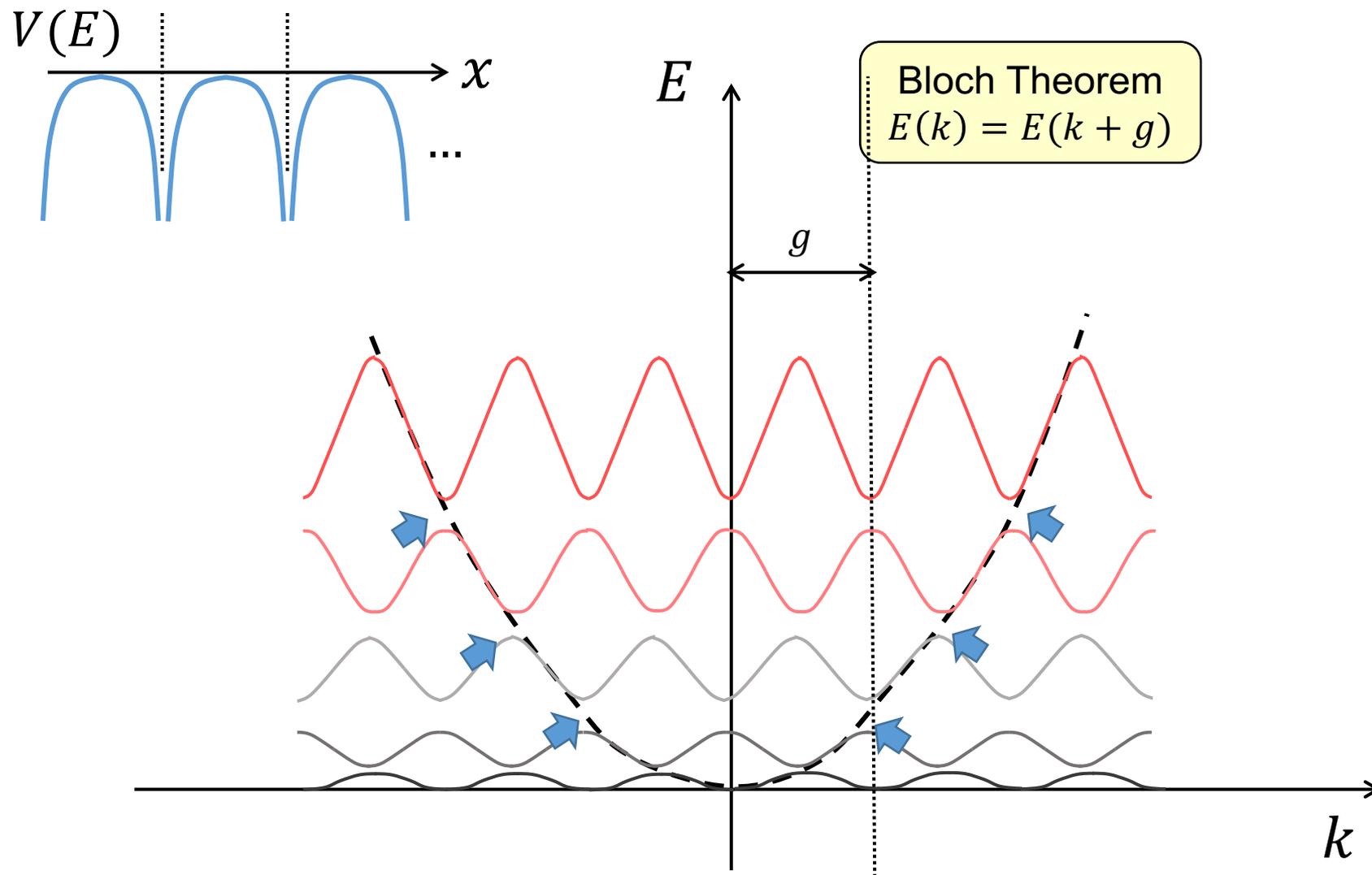
Photon-counting Detector

Expensive to fabricate

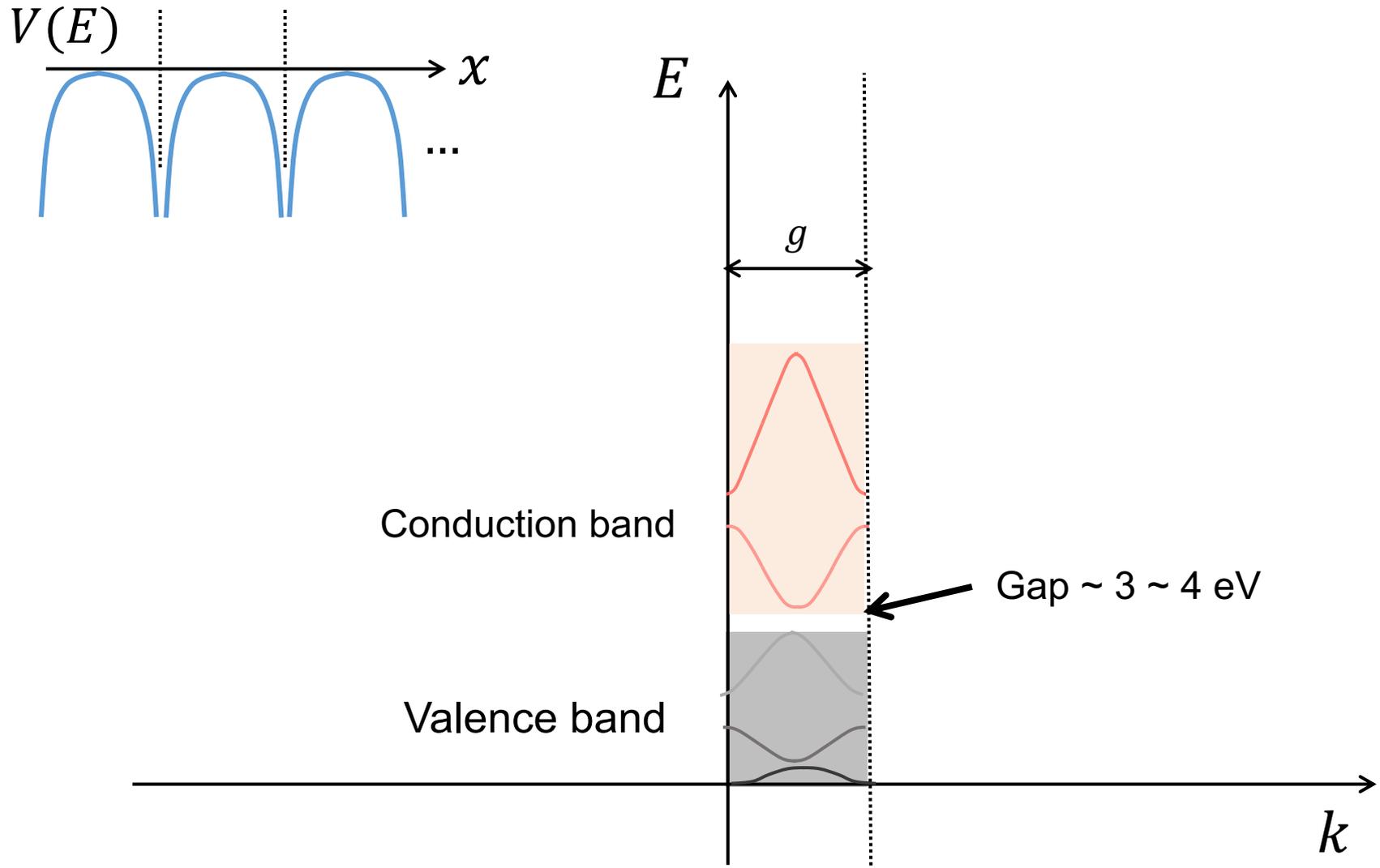
E-k diagram of an bounded electron



E-k diagram



E-k diagram



Charge carrier mobility

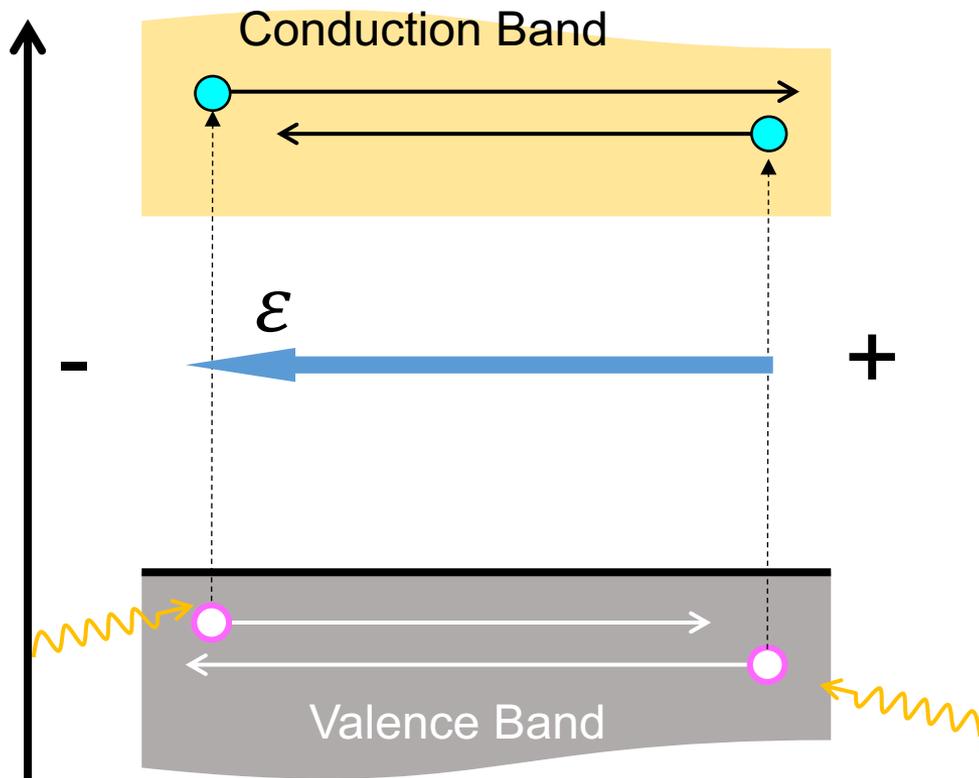
$$v = -\mu\epsilon_{\text{reduced electric field}}$$

$$\epsilon \uparrow, \mu \uparrow, v \uparrow$$

☺ Collection time

☺ Recombination

Energy

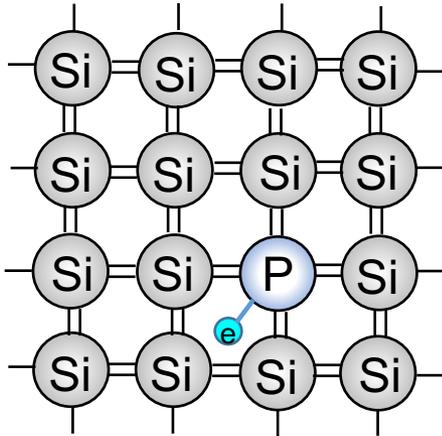


Material	$\mu_n [cm^2 / (V \cdot s)]$	$\mu_p [cm^2 / (V \cdot s)]$
c-Si	1400	480
a-Si	1	0.005
CdTe	1100	100

Doping effect

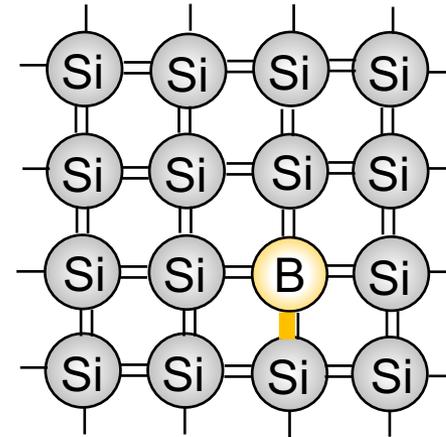
N-type

Donate electron



P-type

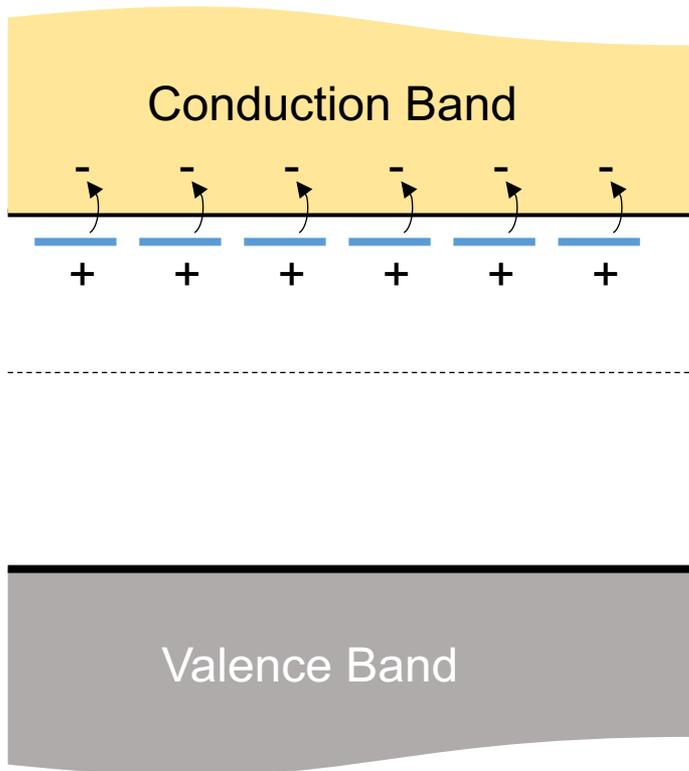
Receive electron



Band structure

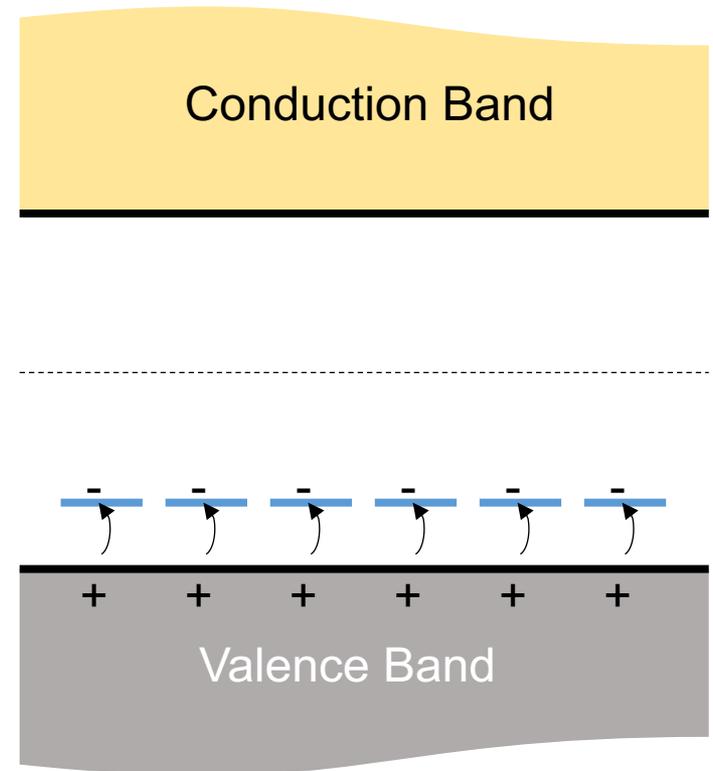
N-type

Donate electron

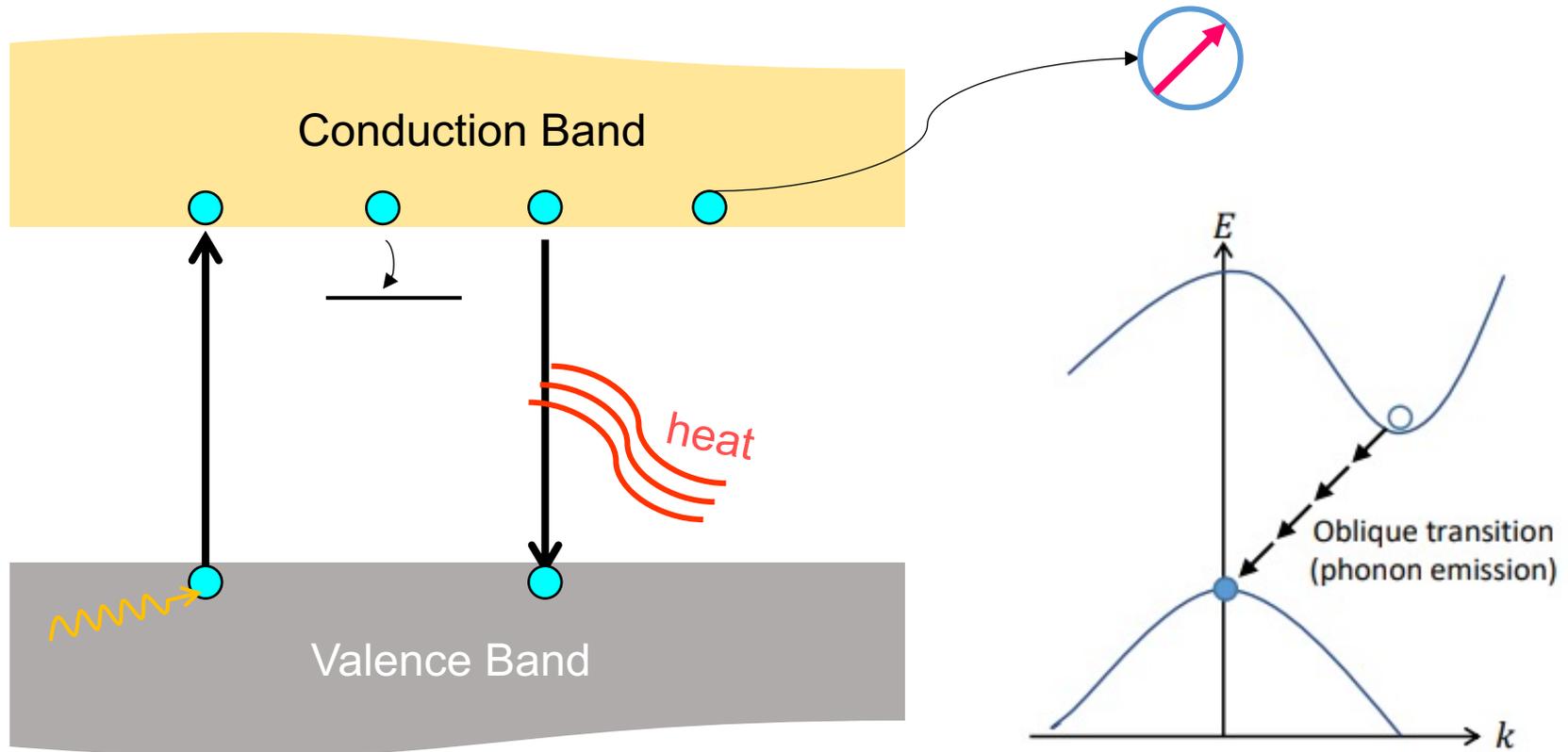


P-type

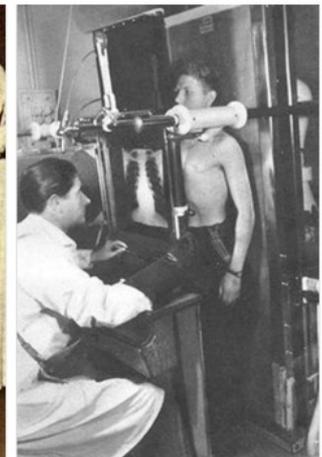
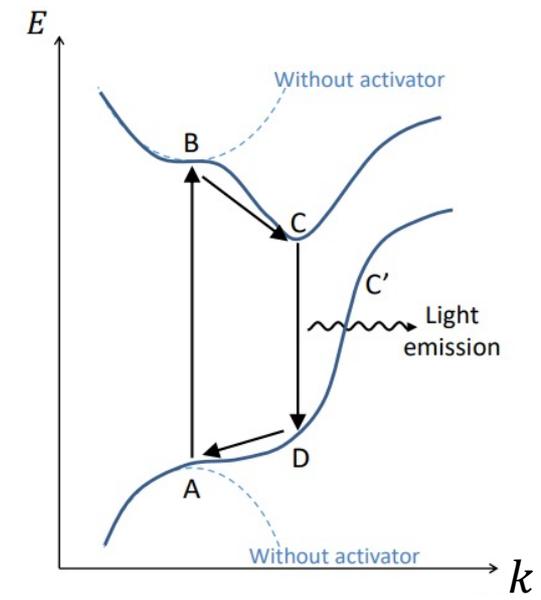
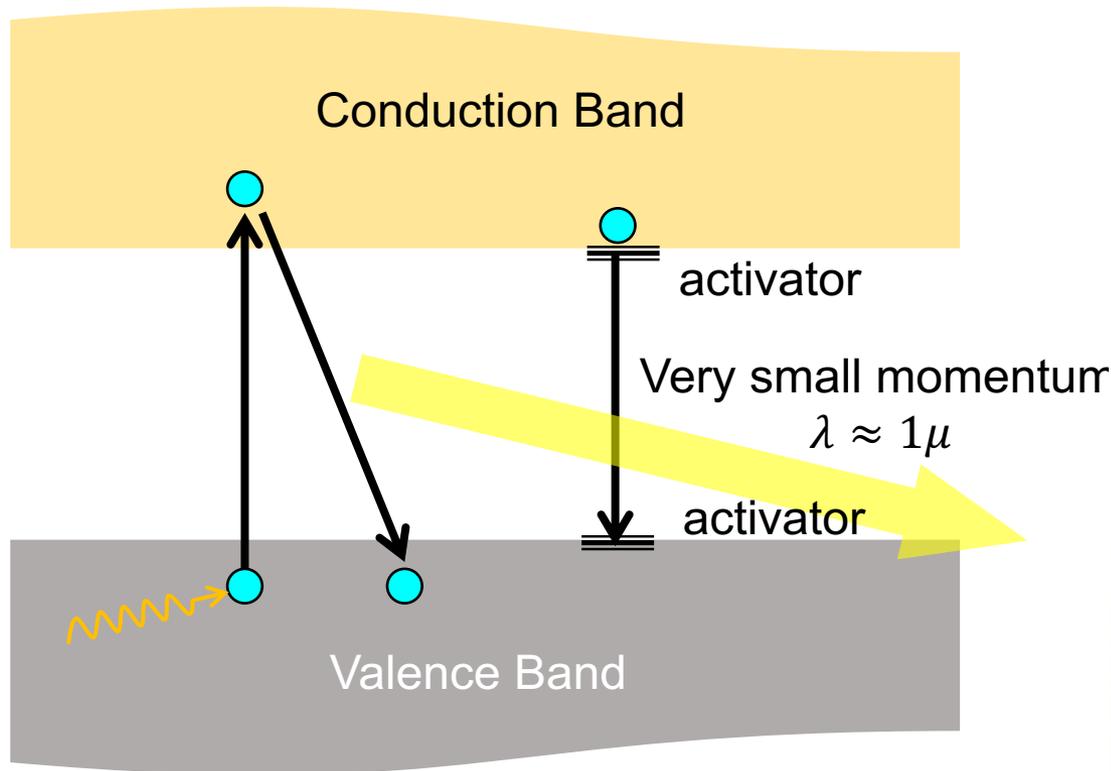
Receive electron



Direct conversion detector

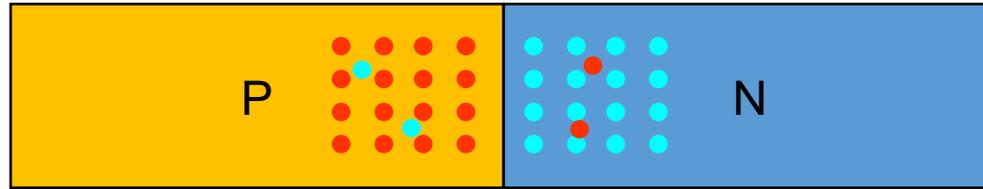


Scintillation detector



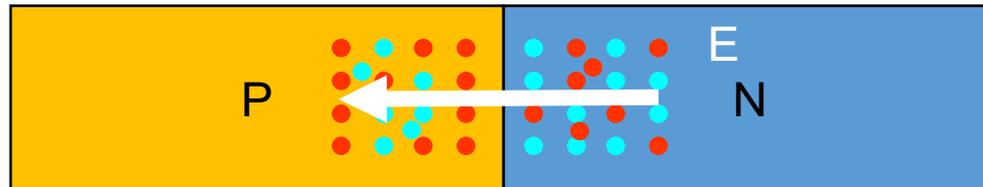
Charge carrier diffusion & drift

holes ● ● electron

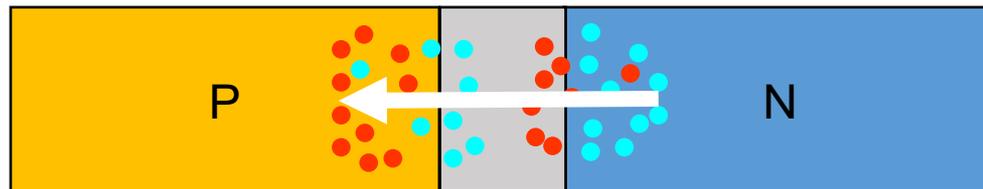


$$J = -eD \frac{\partial n}{\partial x}$$

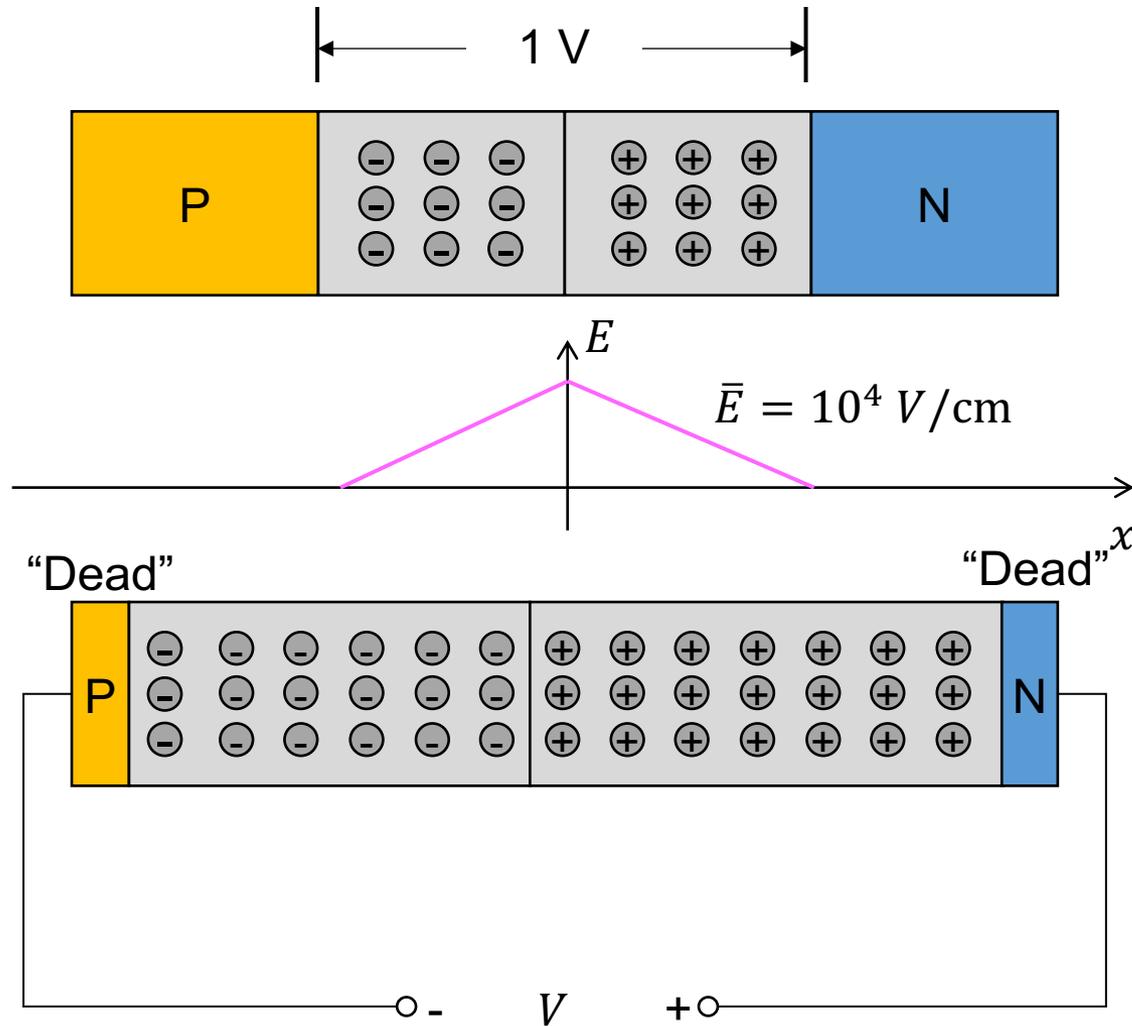
density gradient



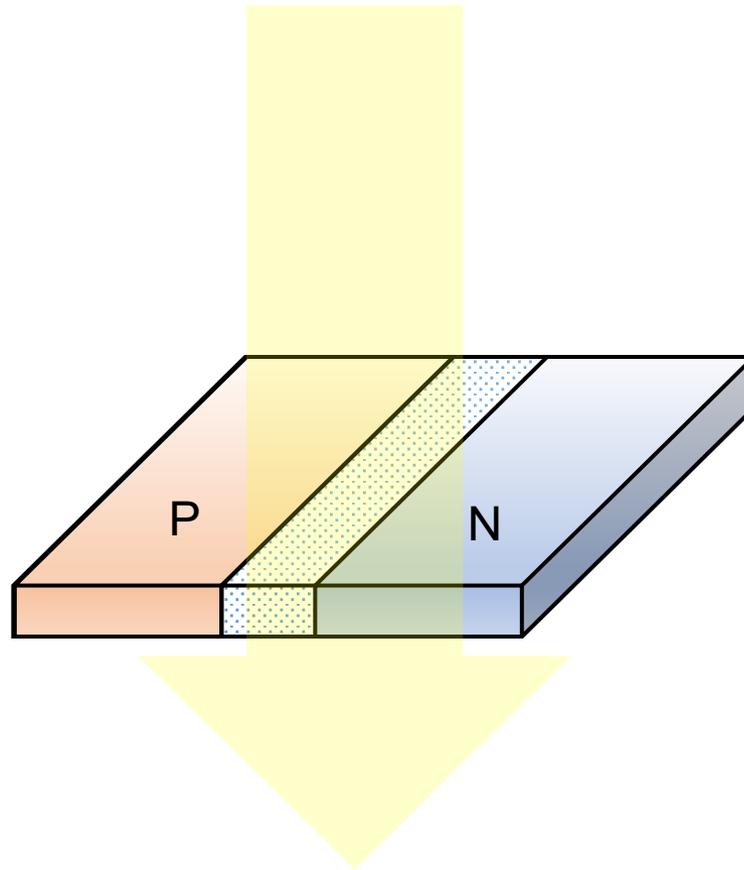
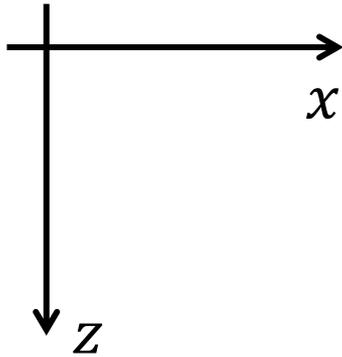
Depletion



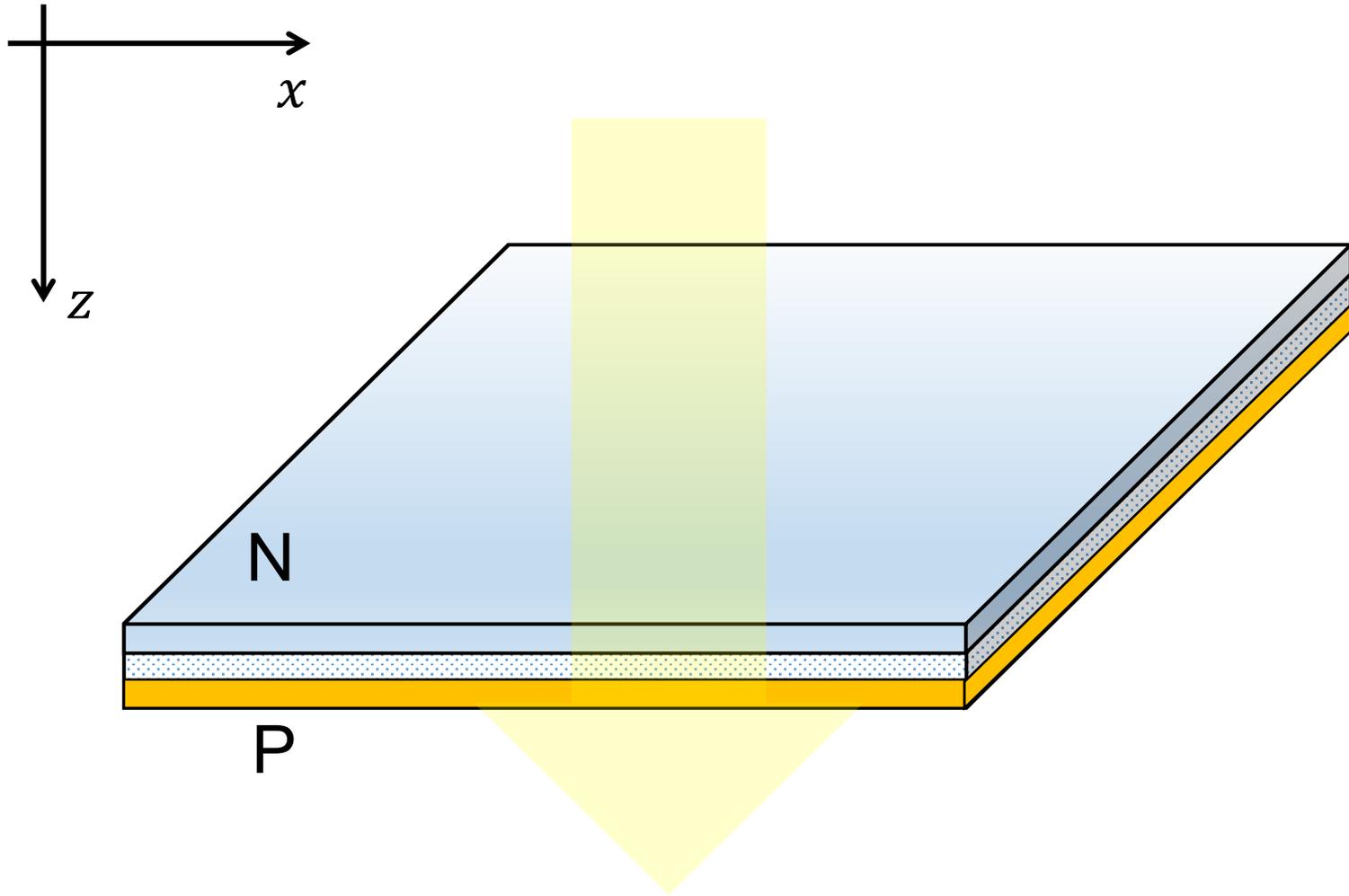
P-N junction



Formation of a p-n junction (I)

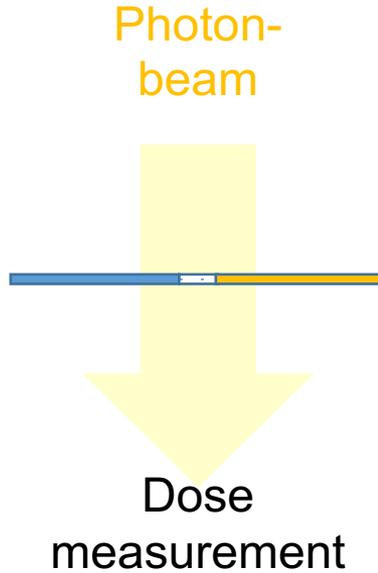


Formation of a p-n junction (II)

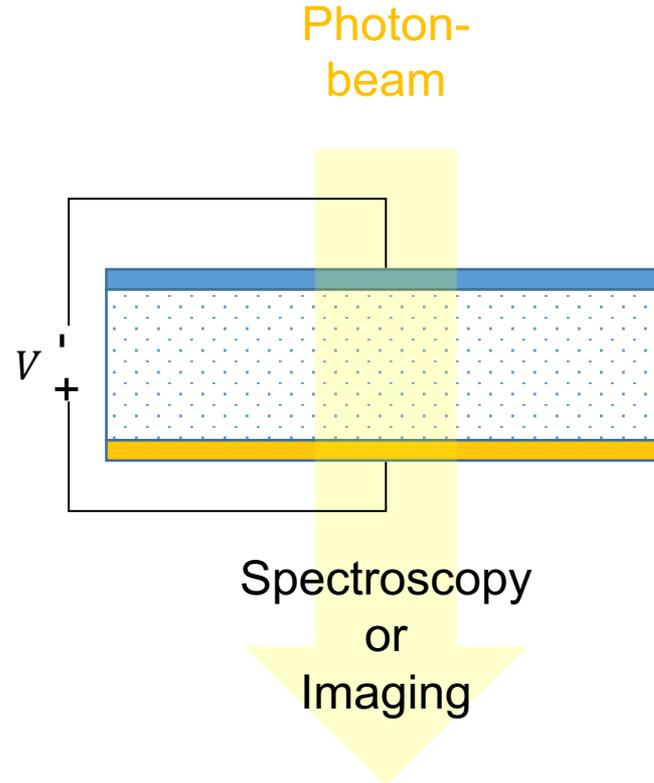


Sensitive Volume Comparison

SIDE VIEW

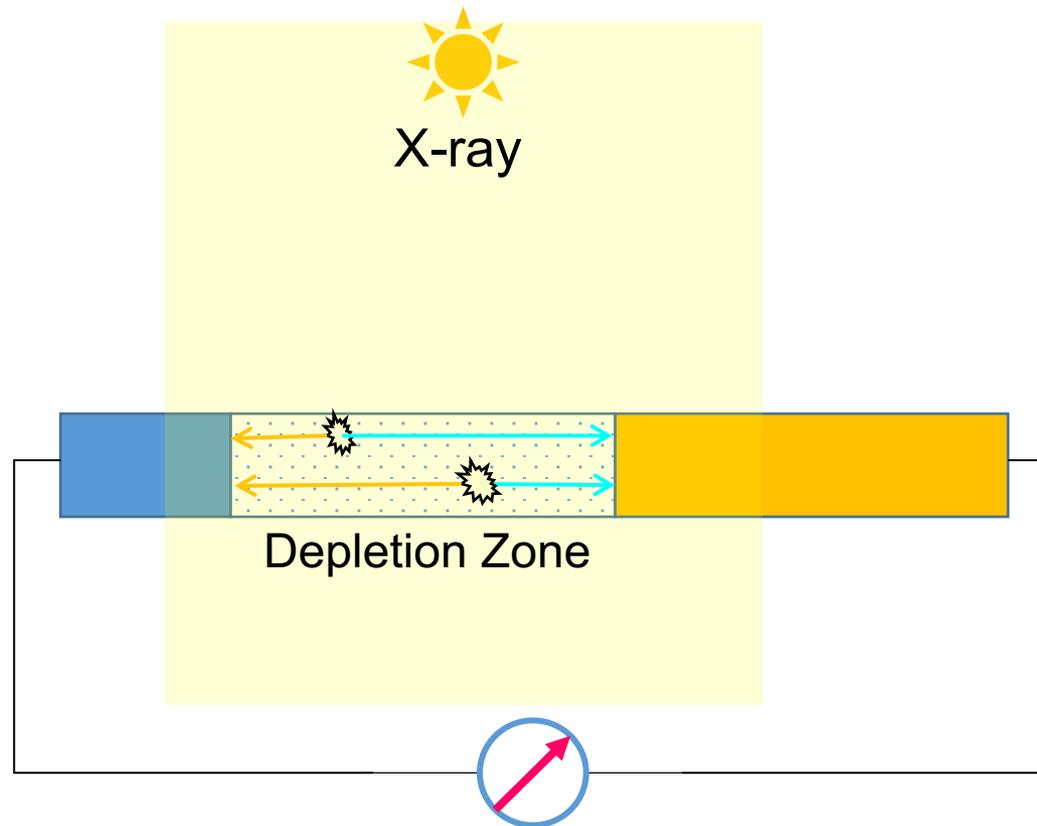


volume averaging ↓
Low SNR ☹️
> ion chamber 😊

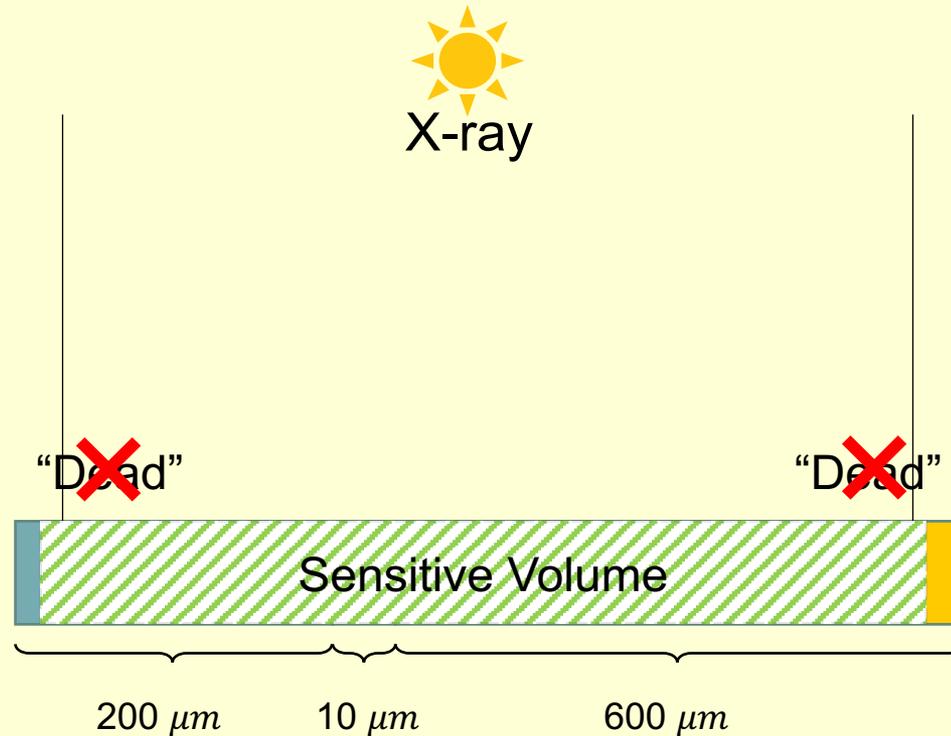


Larger area, efficiency ↑
not enough to stop ☹️
volume average along z ↑

“Dose diode”



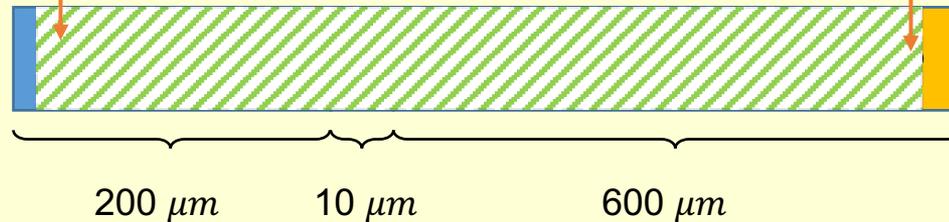
Cannot explain dose rate, temperature dependence very well



- Charge collected
 - \propto Charge created (relatively constant, not all)
 - \propto Sensitive volume (assume uniform dose profile)
 - Influenced by the diffusion length.

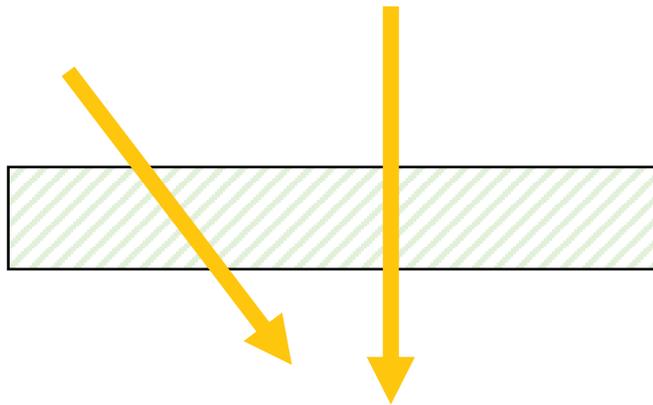


Impact factor: Minority charge carrier diffusion length



***p* type has less dose rate dependence**

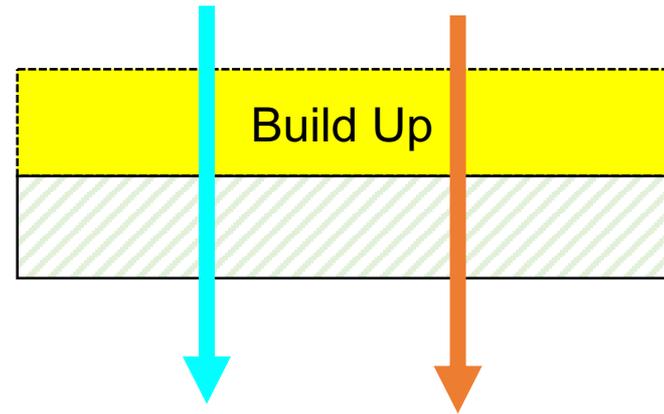
- Dose rate \uparrow , indirect recombination \downarrow , charge carriers \uparrow , SNR \uparrow
- ~~Dose rate \uparrow , direct recombination \uparrow , diffusion length \downarrow , SNR \downarrow~~
- Temperature \uparrow , kinetic energy \uparrow , diffusion length \uparrow , SNR \uparrow



Oblique path absorption \uparrow

Solution

Placement



Low energy absorption > High energy

Solution

energy-specific diode

- Advantage

- High SNR, instant readout
- Less volume average
- Tissue-equivalent

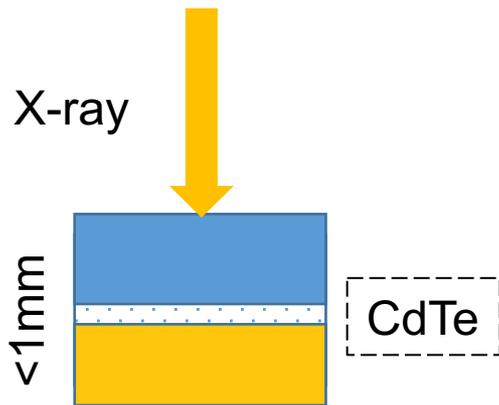
- Disadvantage

- Dose rate dependence
- Temperature dependence
- Energy dependence (buildup)
- Radiation Damage decreases sensitivity
- Not so clinically versatile

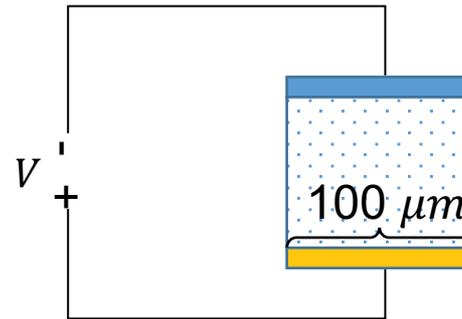
“Imaging diodes”

stop 95% kV x-ray

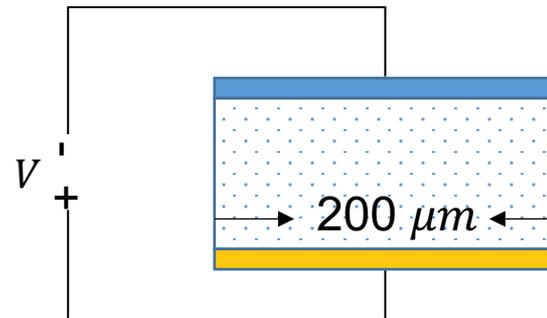
1.7 mm CdTe
55 mm Silicon



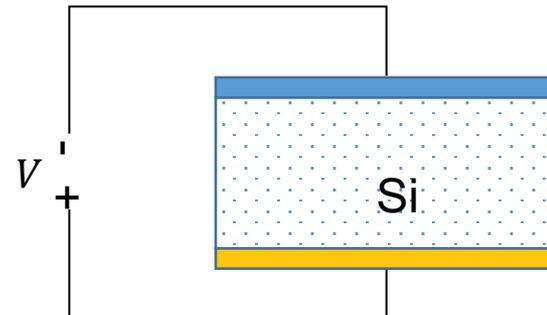
P-N junction
without bias
(face-on)



Reverse bias
Detector efficiency \uparrow
Thickness \uparrow , SNR \uparrow

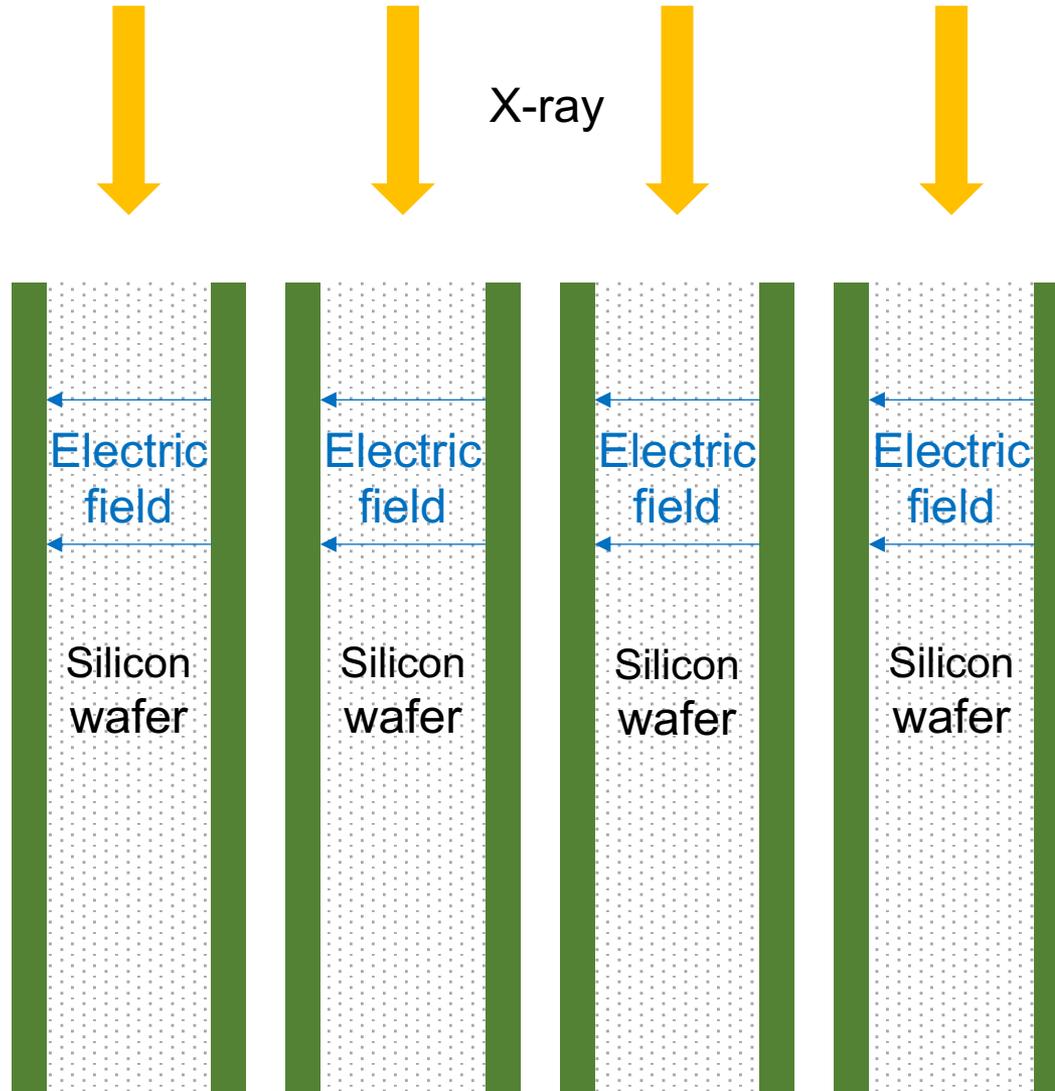


Spatial resolution tradeoff
Sensitive area \uparrow SNR \uparrow

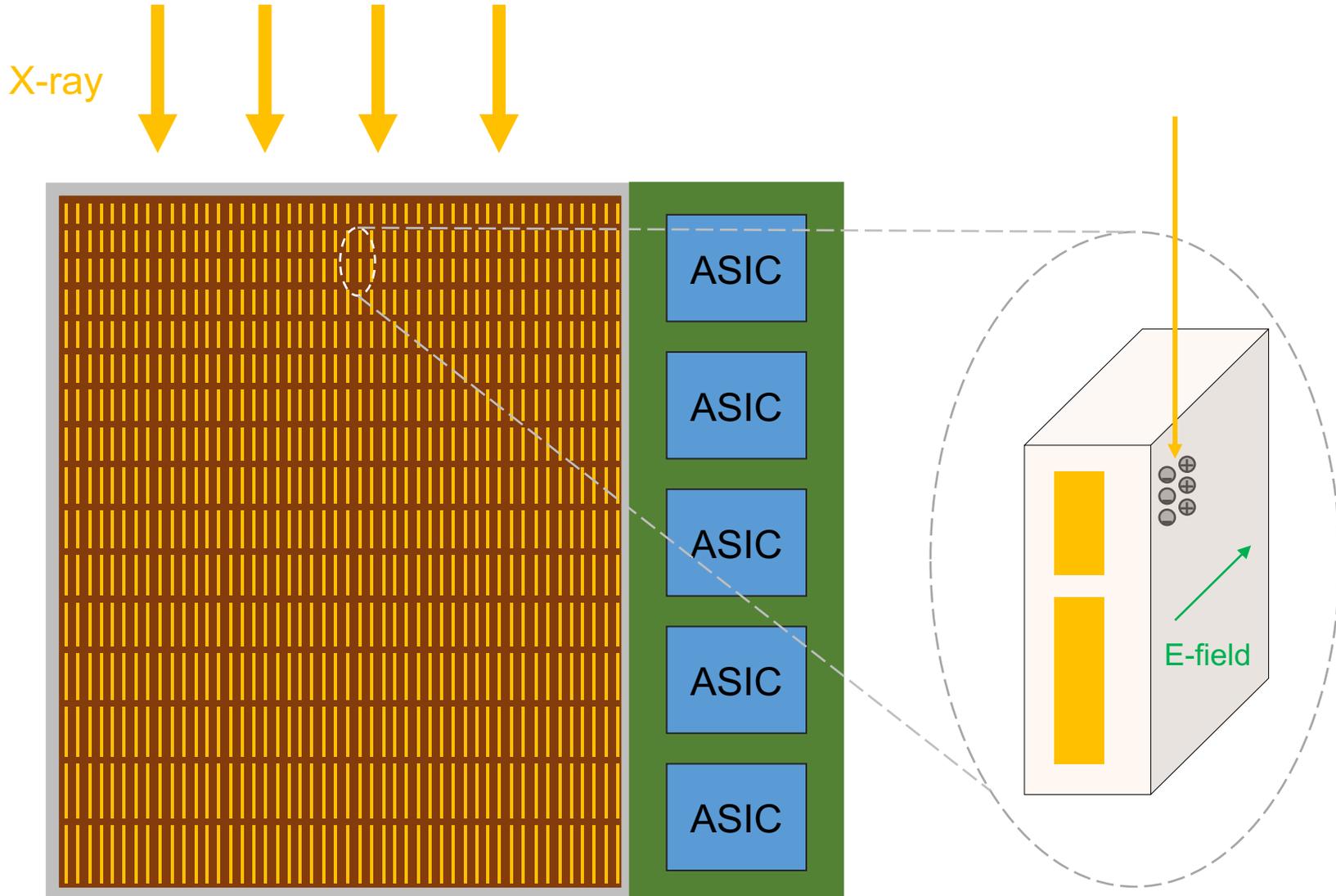


Charge mobility \uparrow
Collected charge \uparrow
Collection time \downarrow 😊
Efficiency \downarrow ☹️

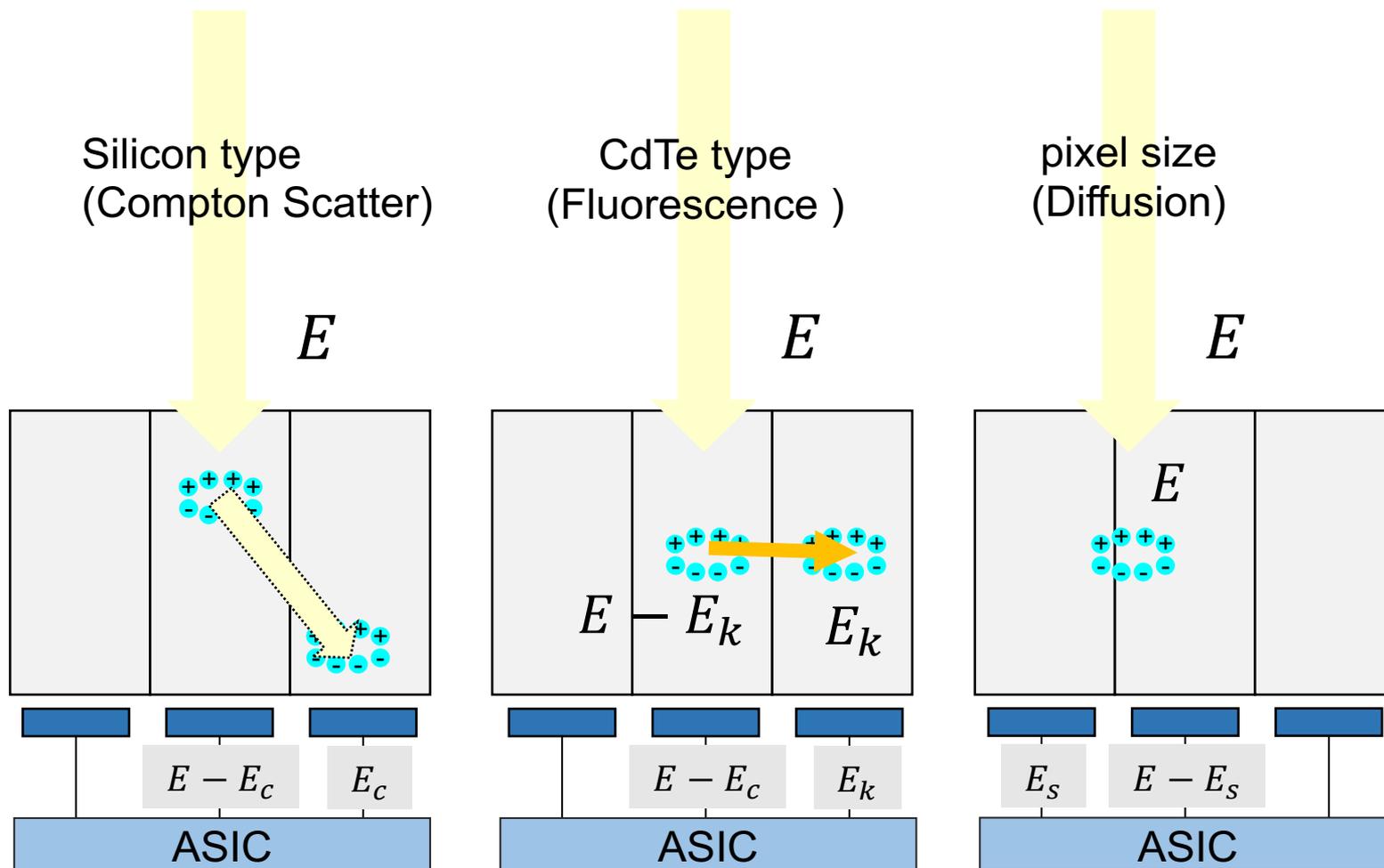
The edge on geometry



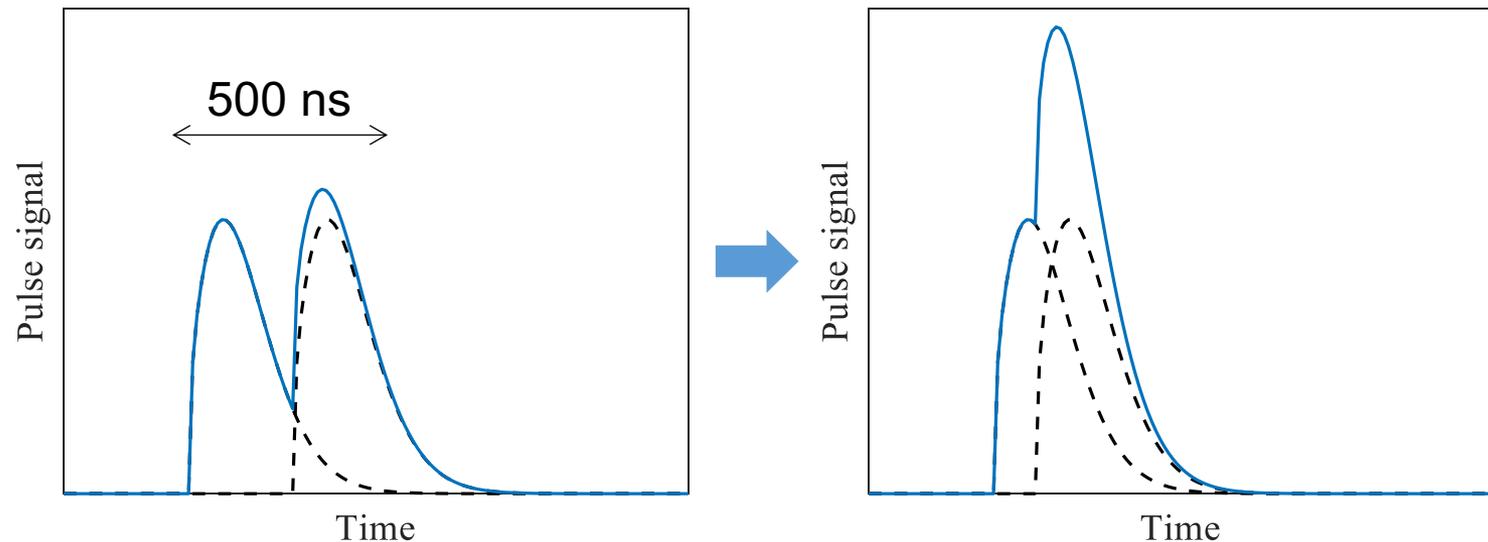
Edge-on detector



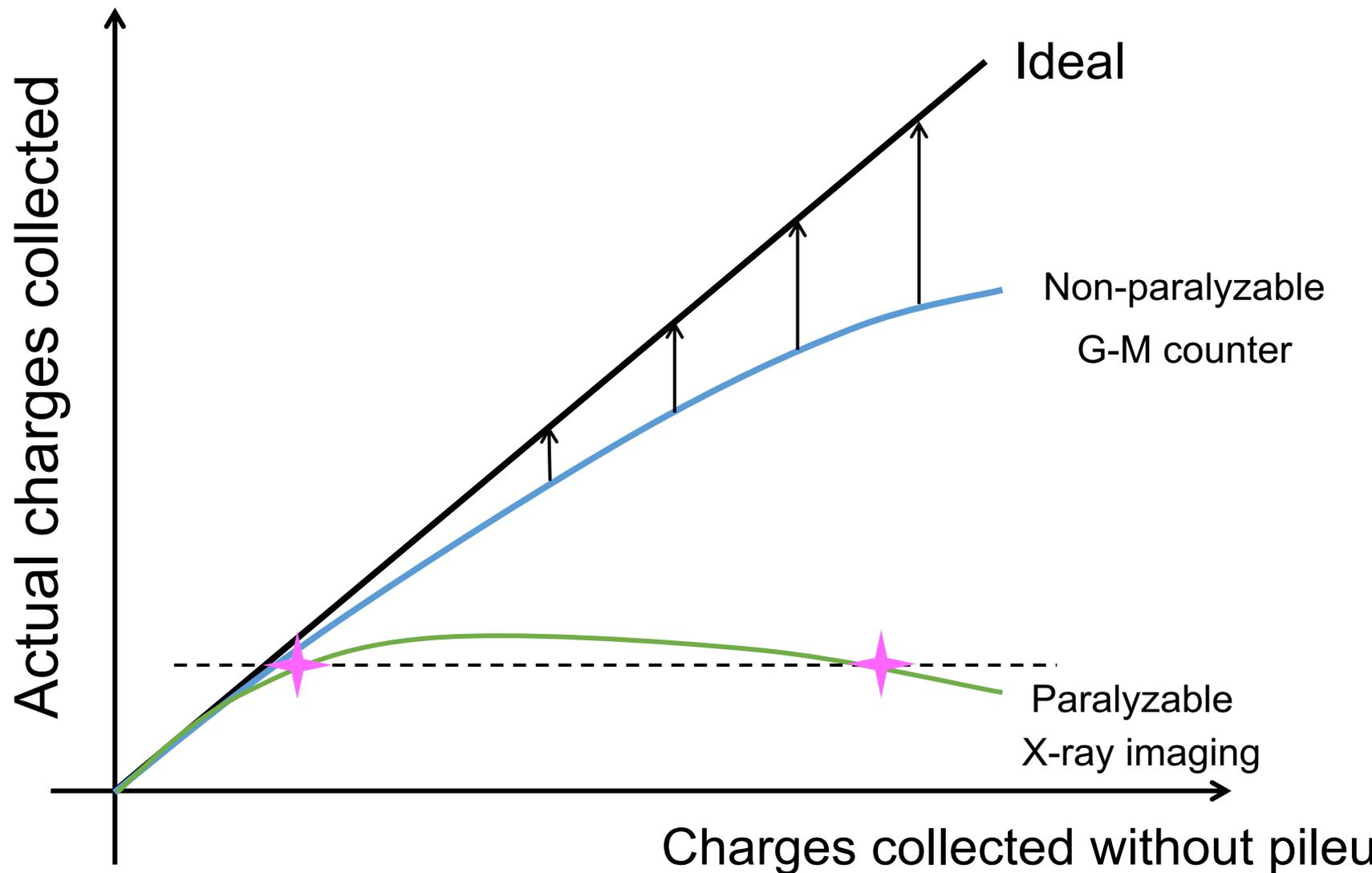
Charge Sharing



- The count rate in x-ray CT imaging is very high!
- Not a concern for dose measurement as the dosimeter works in the continuous mode.



Pulse Pileup Correction



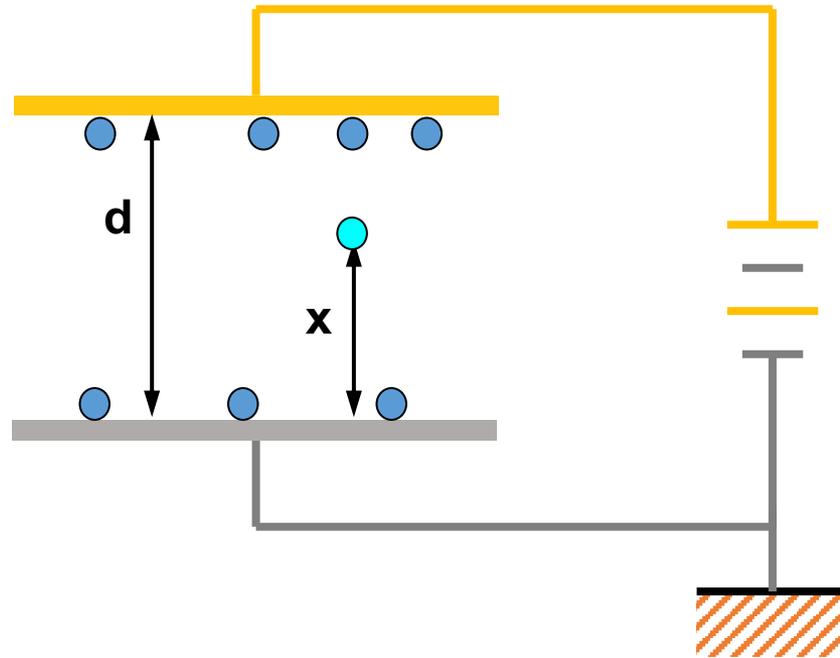
- Semiconductor detectors have different working conditions, which decide their characteristics specific to imaging or dosimetry purposes.



Robert Wood Johnson University Hospital | **RWJBarnabas HEALTH**

Contact: cz453@cinj.Rutgers.edu

Shockley-Ramo theory



Overview of air chambers

